

Experiments on deflection of charged particles using silicon crystals at REFER ring (Hiroshima University) and Proton Synchrotron (KEK)

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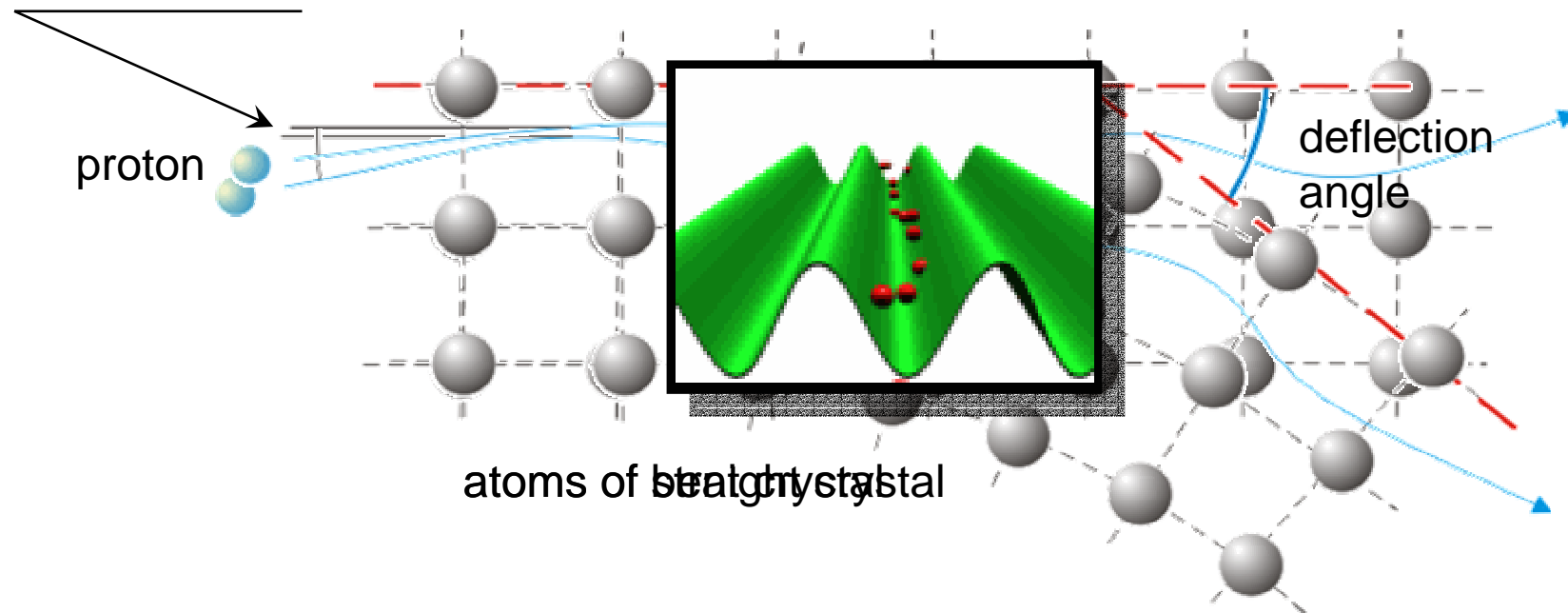
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1. Introduction to the channeling effect
2. Motivation
3. Experiment on electron beam deflection
(REFER, Hiroshima University)
4. Experiment on proton beam deflection
(Proton Synchrotron, KEK)
5. Conclusion

Introduction

(channeling effect)

θ – angle of incident particle to the crystallographic plane



$\theta < \text{Lindhard angle} \rightarrow \text{channeling effect}$

$\theta > \text{Lindhard angle} \rightarrow \text{no channeling effect}$

Motivation

Application to deflection of high energy (50 GeV) and high intensity proton beam at J-PARC (Japan Proton Accelerator Research Complex):

- beam splitting in a slow-extraction beam,
- beam collimator,
- slow beam extraction from the synchrotron in the future.

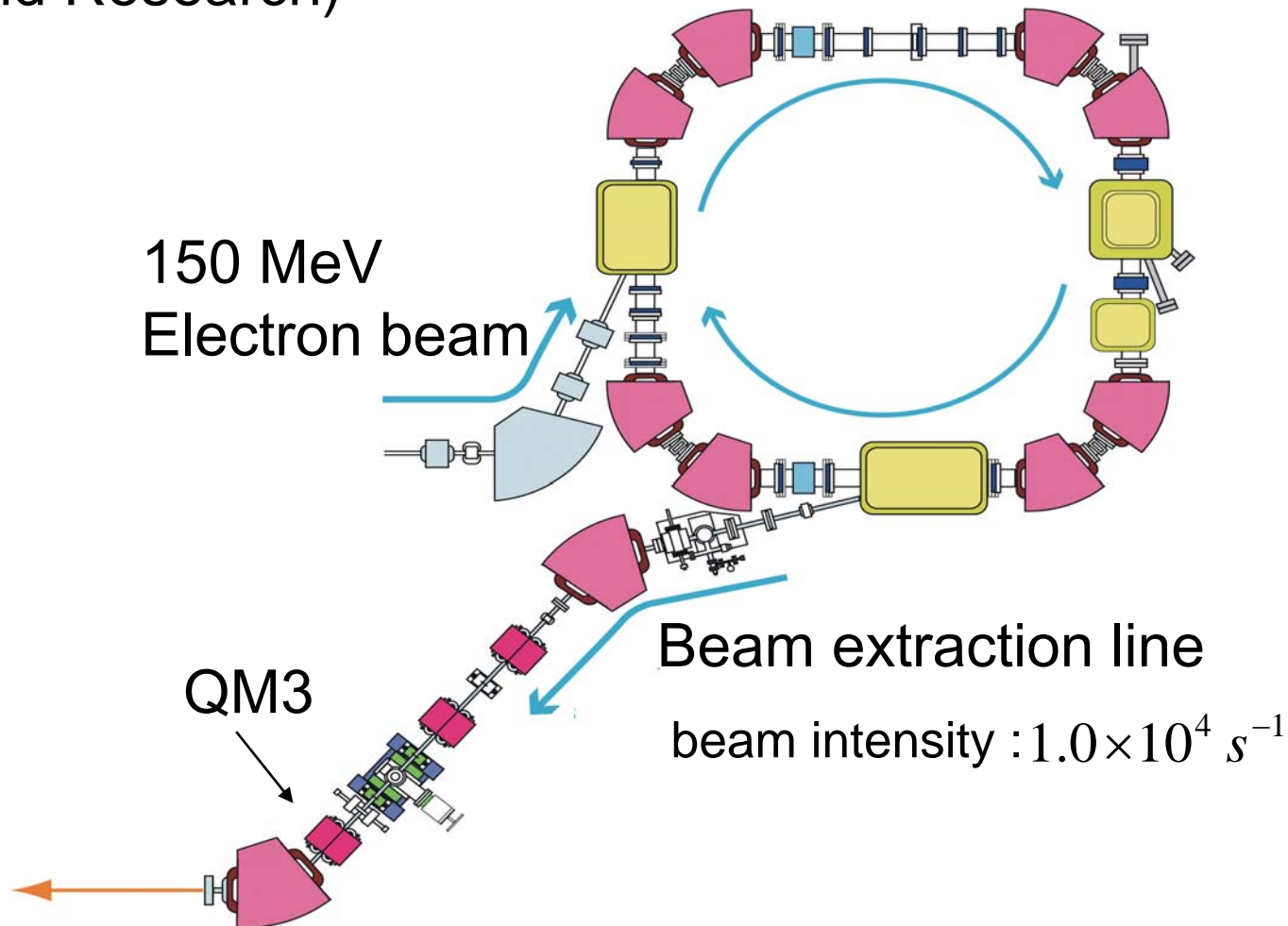
Collimation of the ultra-low emittance beam at ILC (International Linear Collider).

Beam extraction from the REFER ring is within the scope.

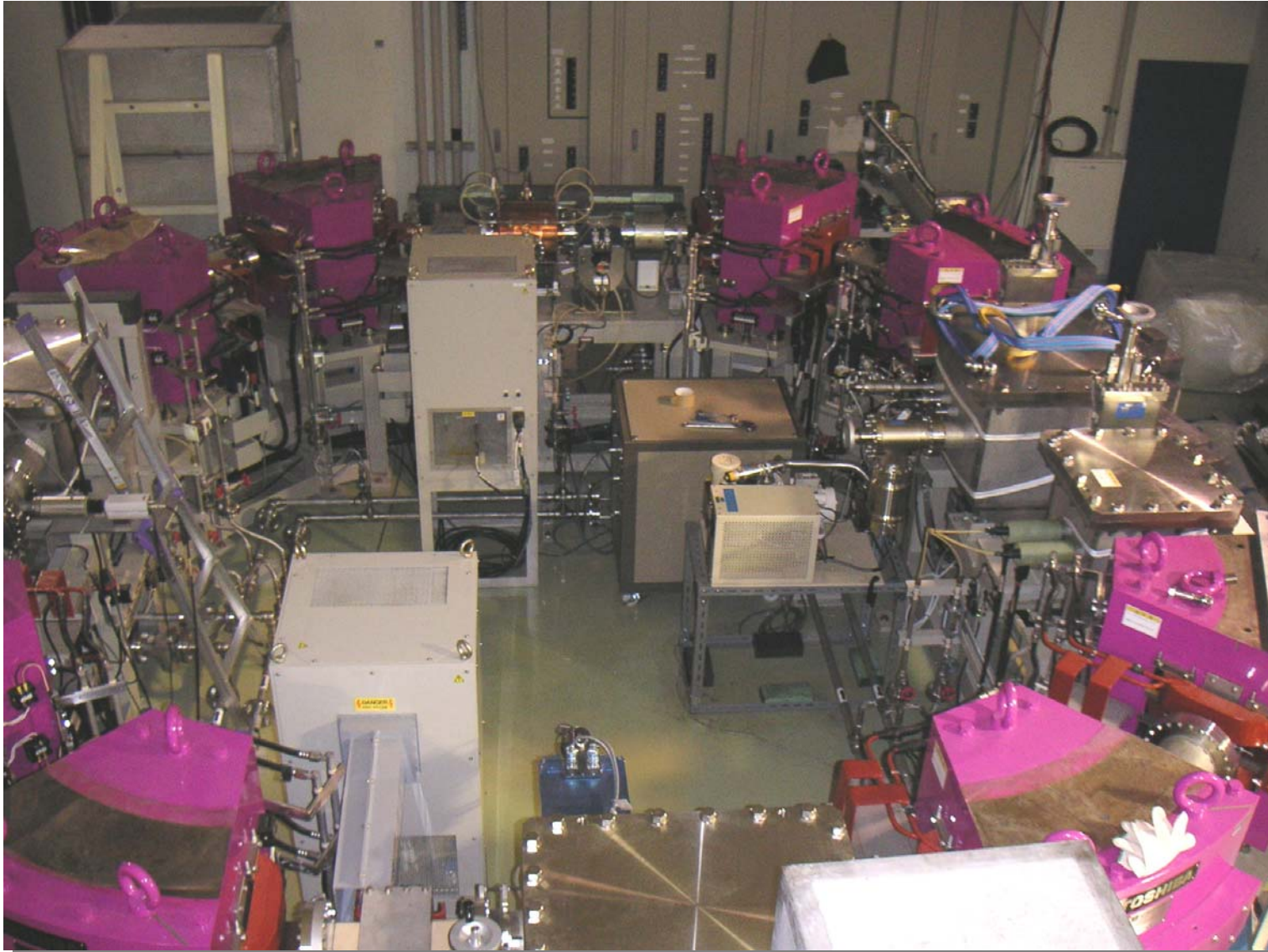
Beam diagnosis by channeling effect (beam divergence and profile).

REFER ring @ Hiroshima University

- REFER (Relativistic Electron Facility for Education and Research)



REFER ring @ Hiroshima University



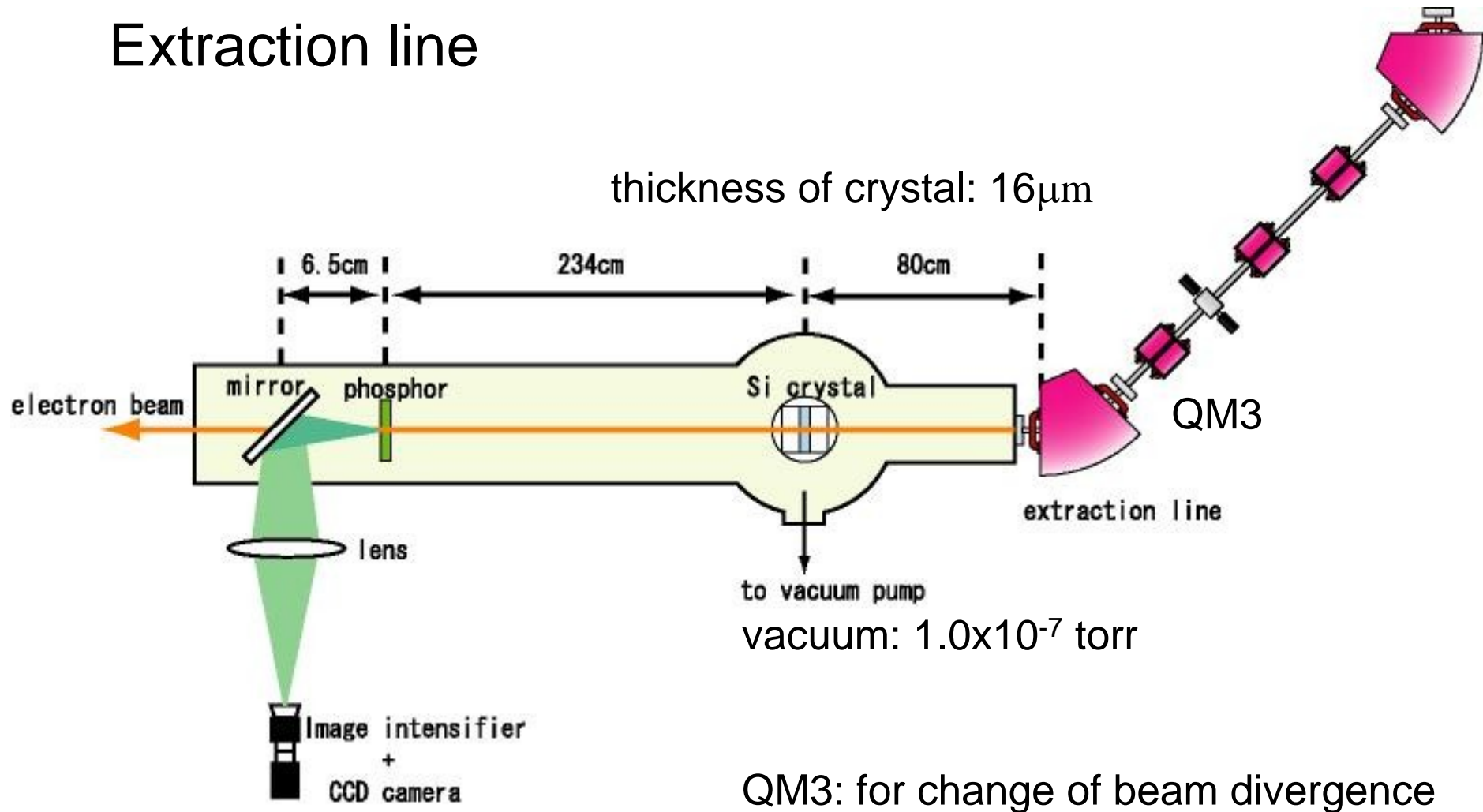
10 July, 2006

Sergey Stokov/ DESY, Hamburg

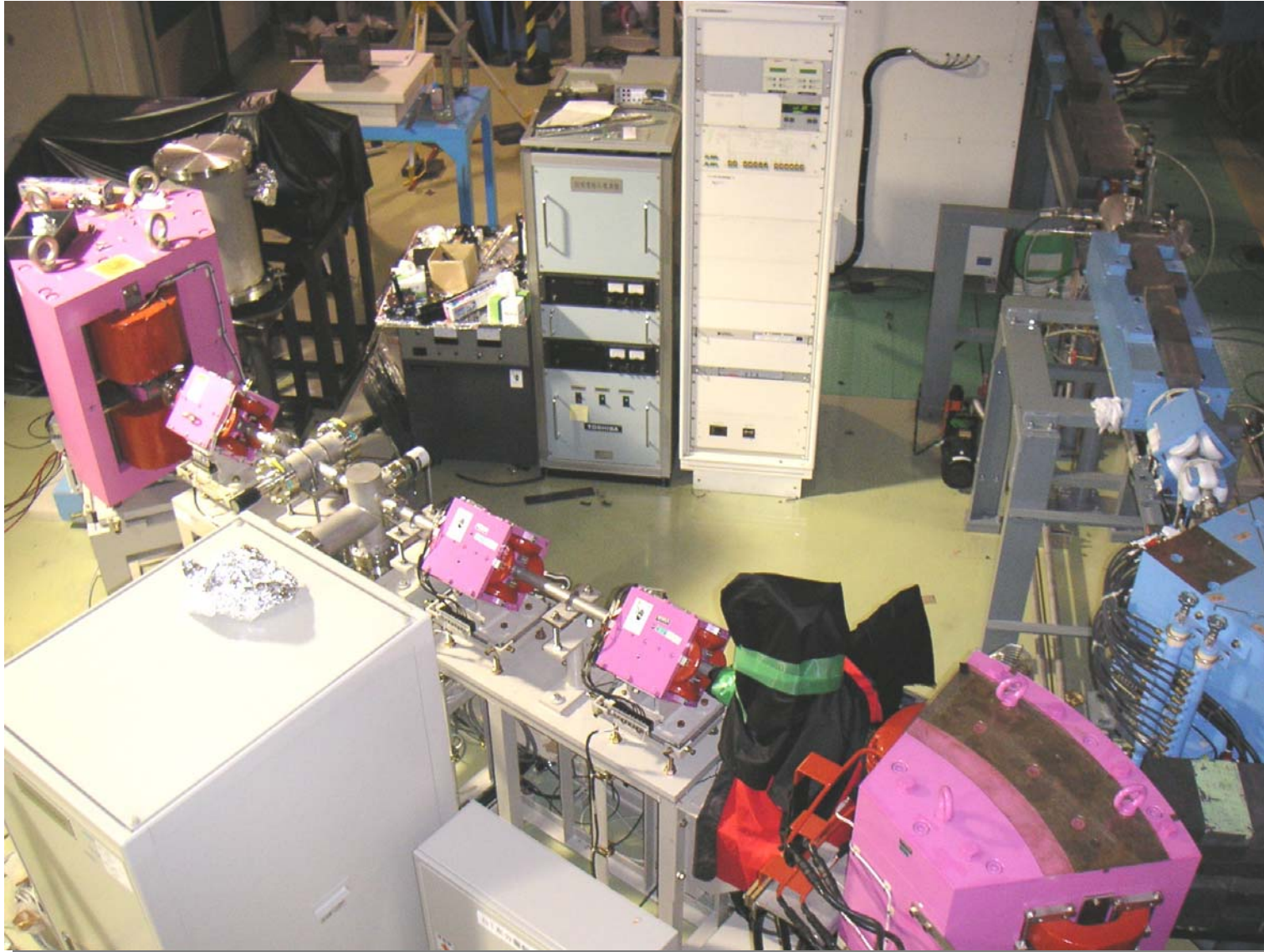
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Experimental setup

Extraction line



Extraction line

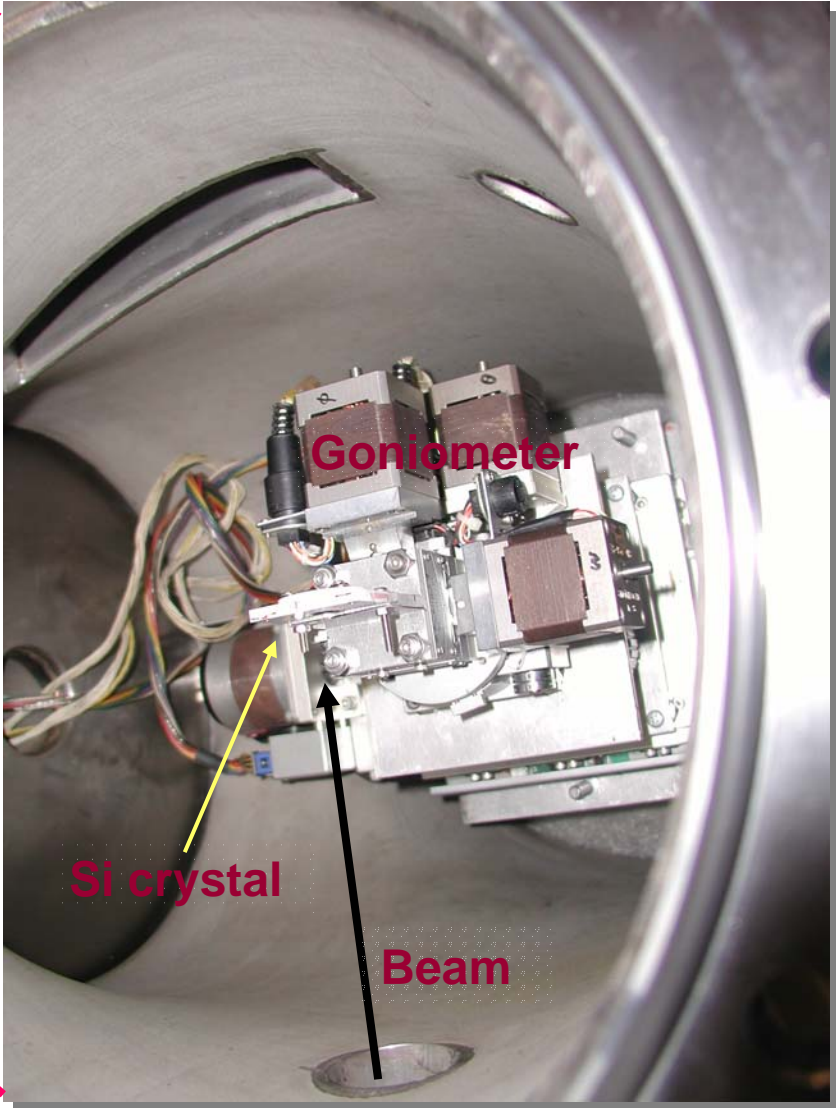
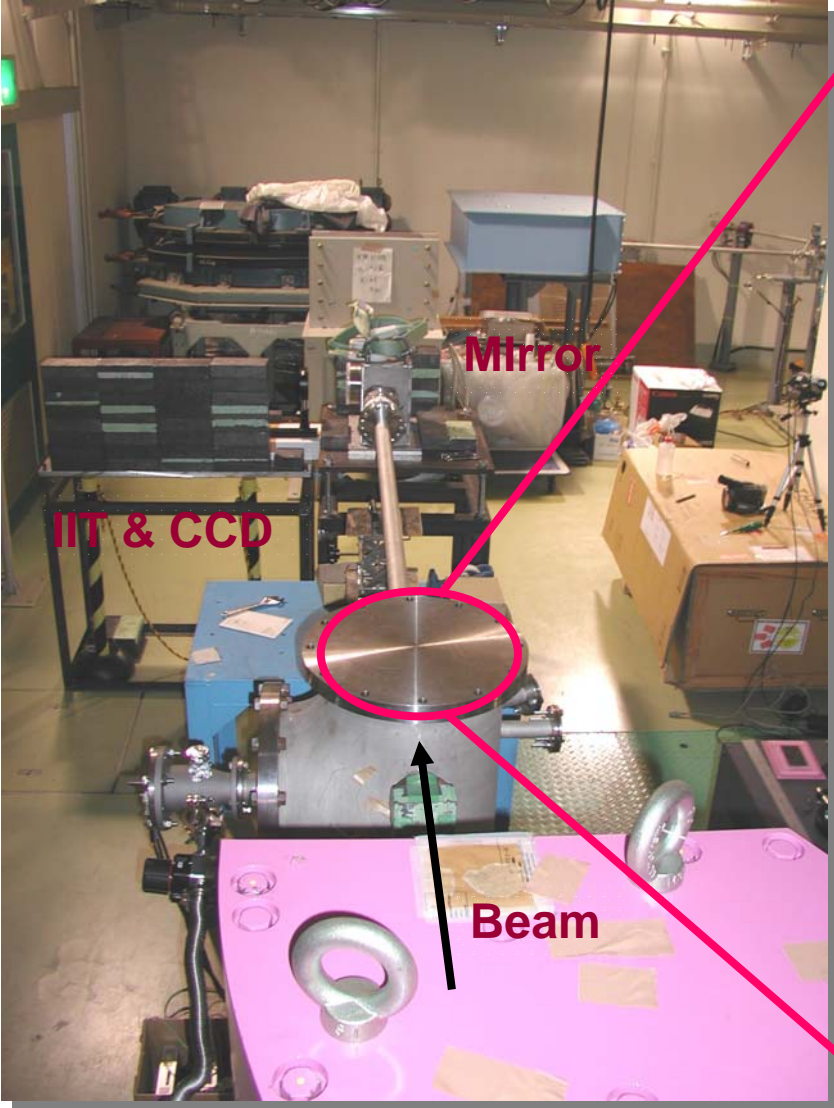


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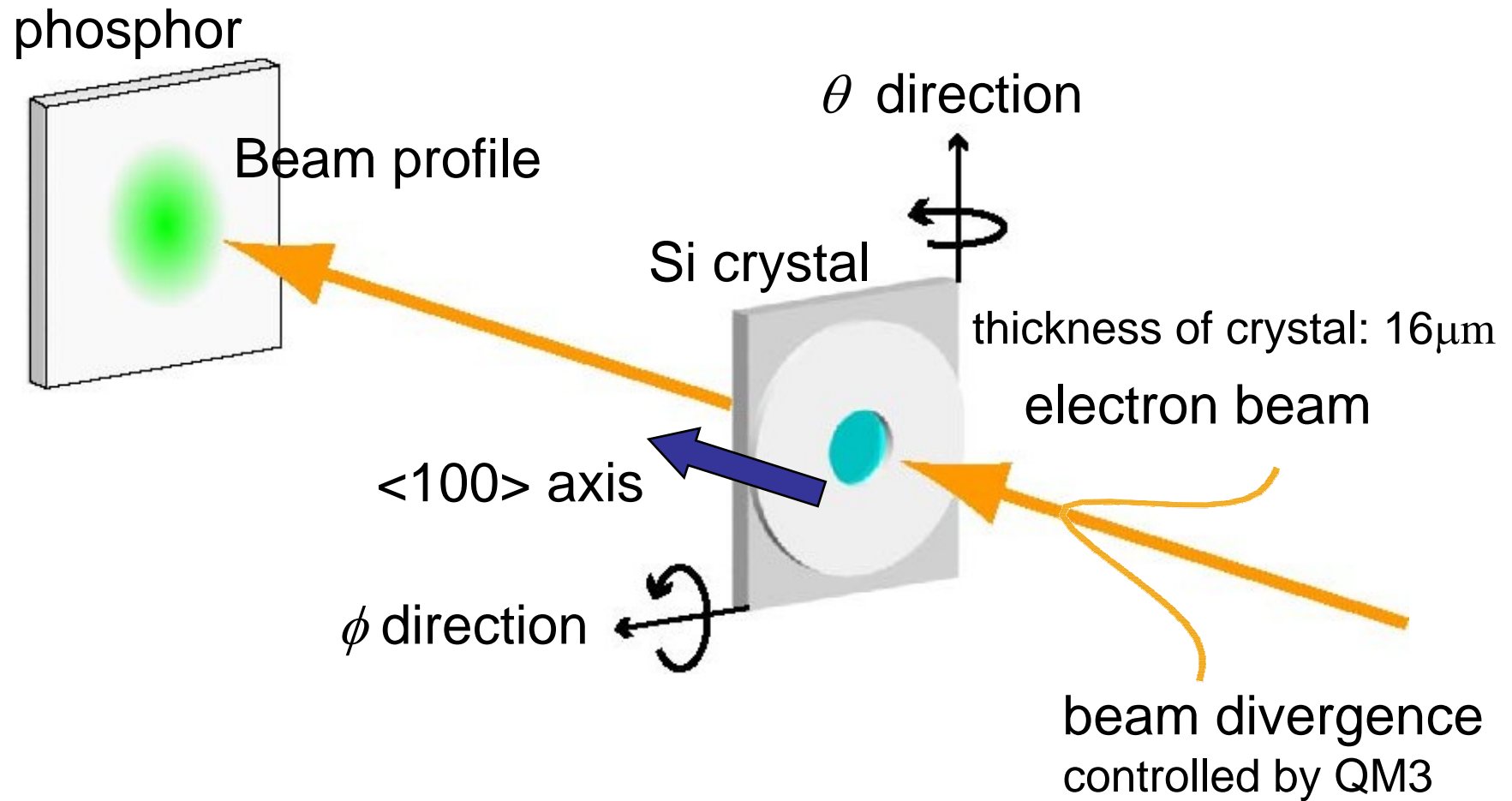
Sergey Stokov/ DESY, Hamburg

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Setup

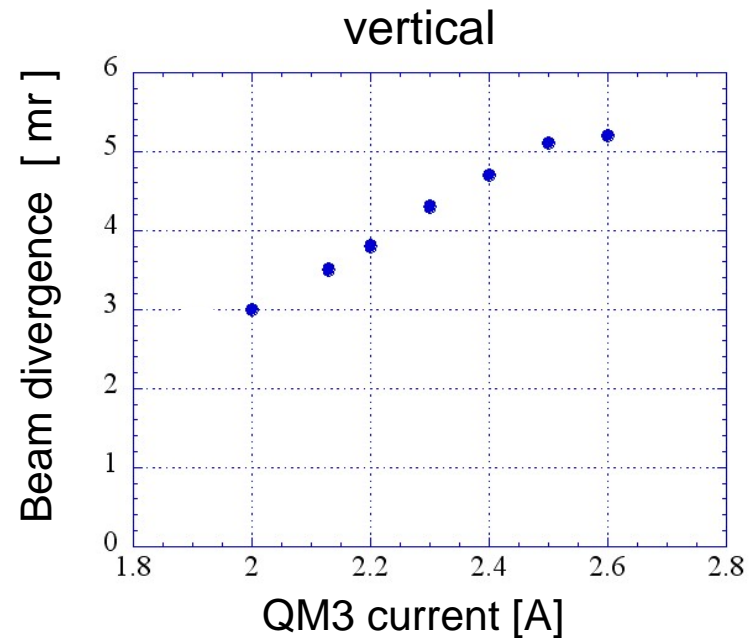
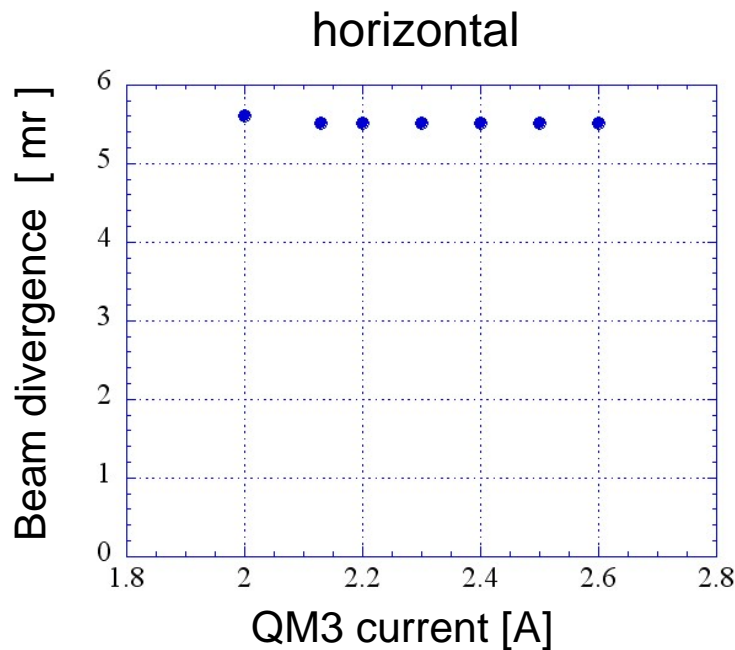
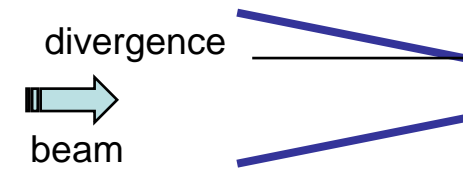


Schematic view of the setup



Experiment: beam divergence

- Beam divergence vs. QM3 current
 (← measured beam profile and optics calculation)

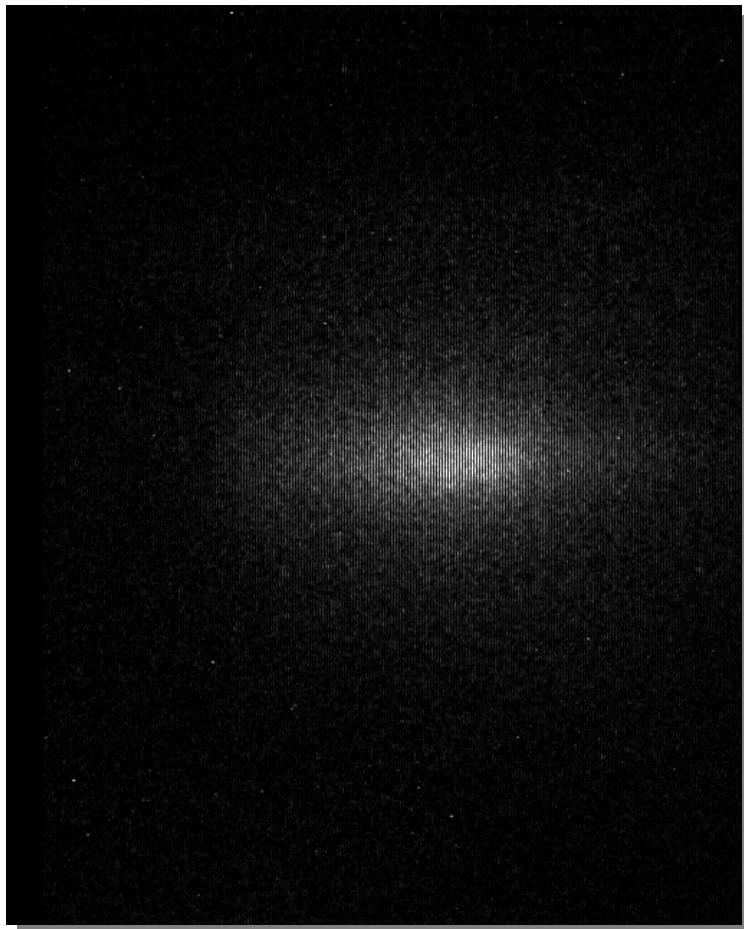


- Vertical angle dependence of the profile is the point.
- Lindhard angle for $\langle 100 \rangle$ axis of Si : 0.7 mr
 – Beam divergence > Lindhard angle

Results: Beam Profiles

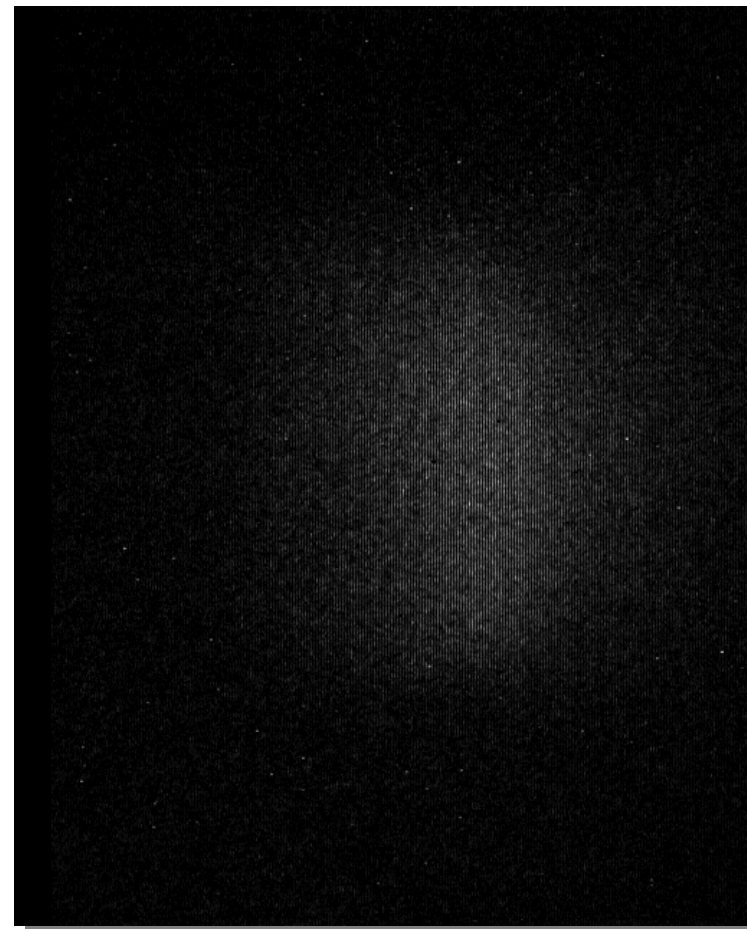
QM3: 2.0A $\theta = 0$, $\phi = -1.5\text{mr}$

Beam divergence: 3.0 mr



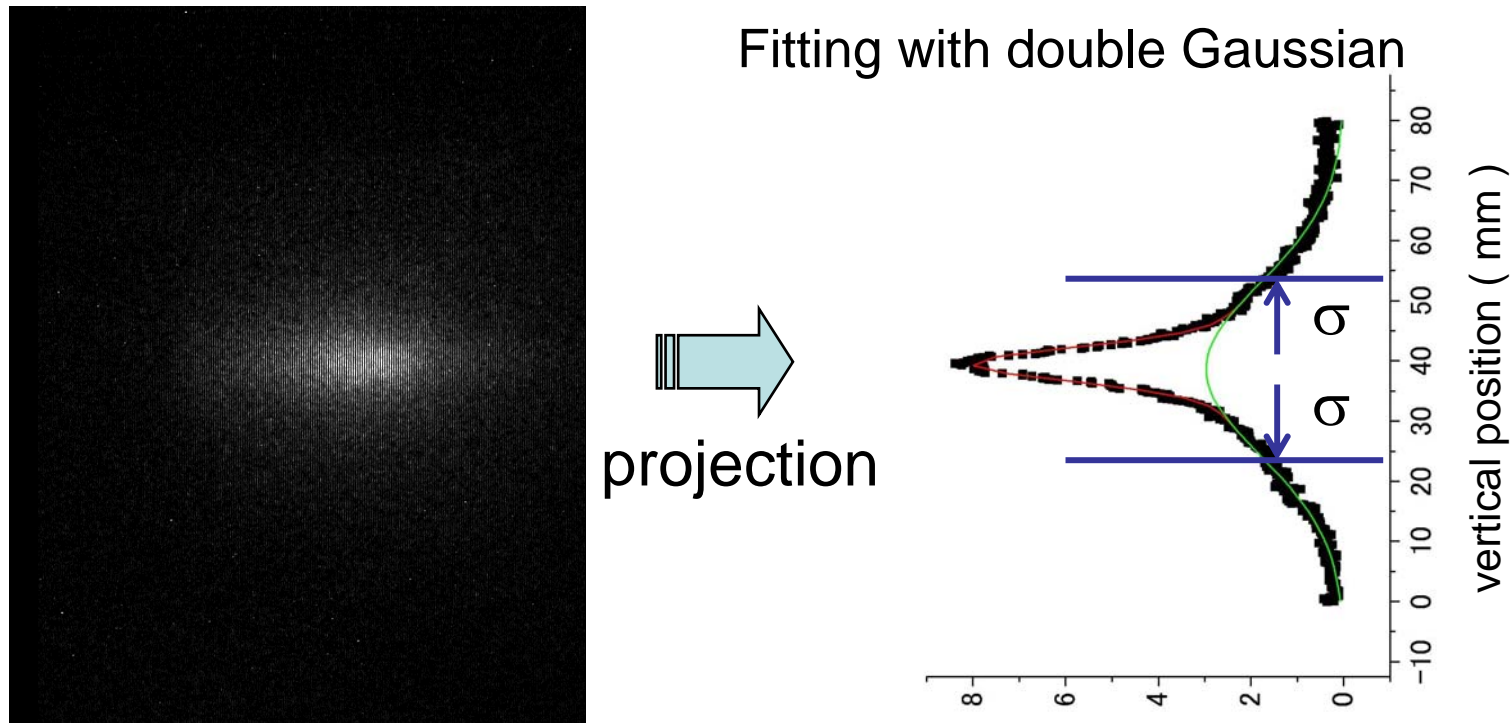
QM3: 2.6A $\theta = 0$, $\phi = -1.5\text{mr}$

Beam divergence: 5.2 mr



Analysis

- Beam divergence (vertical): 3.0 mr QM3: 2.0 A



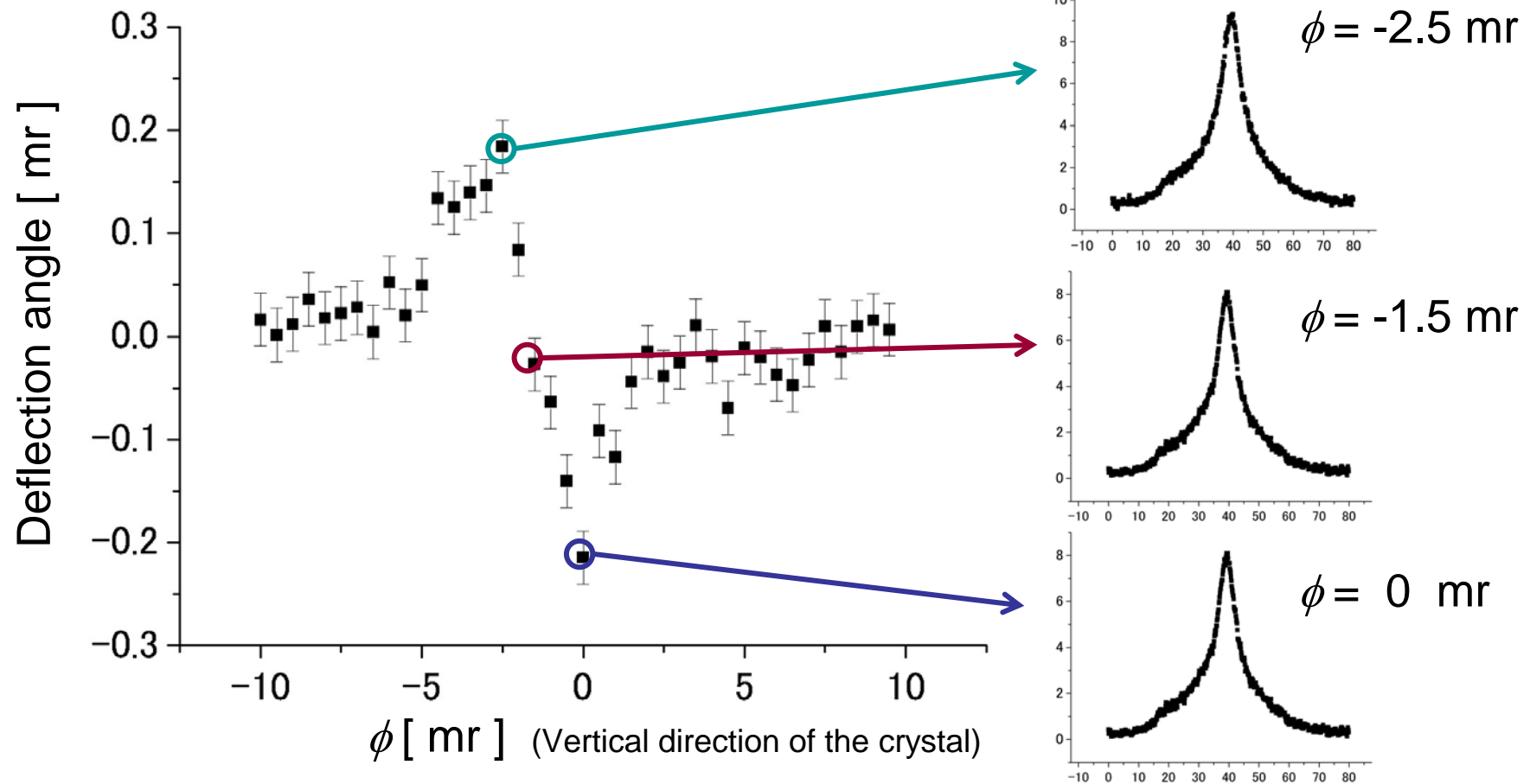
Beam center \equiv weighted average in 2σ region

Results

(1)

- Beam divergence (vertical) : 3.0 mr $\theta=0$ mr (QM3: 2.0 A)

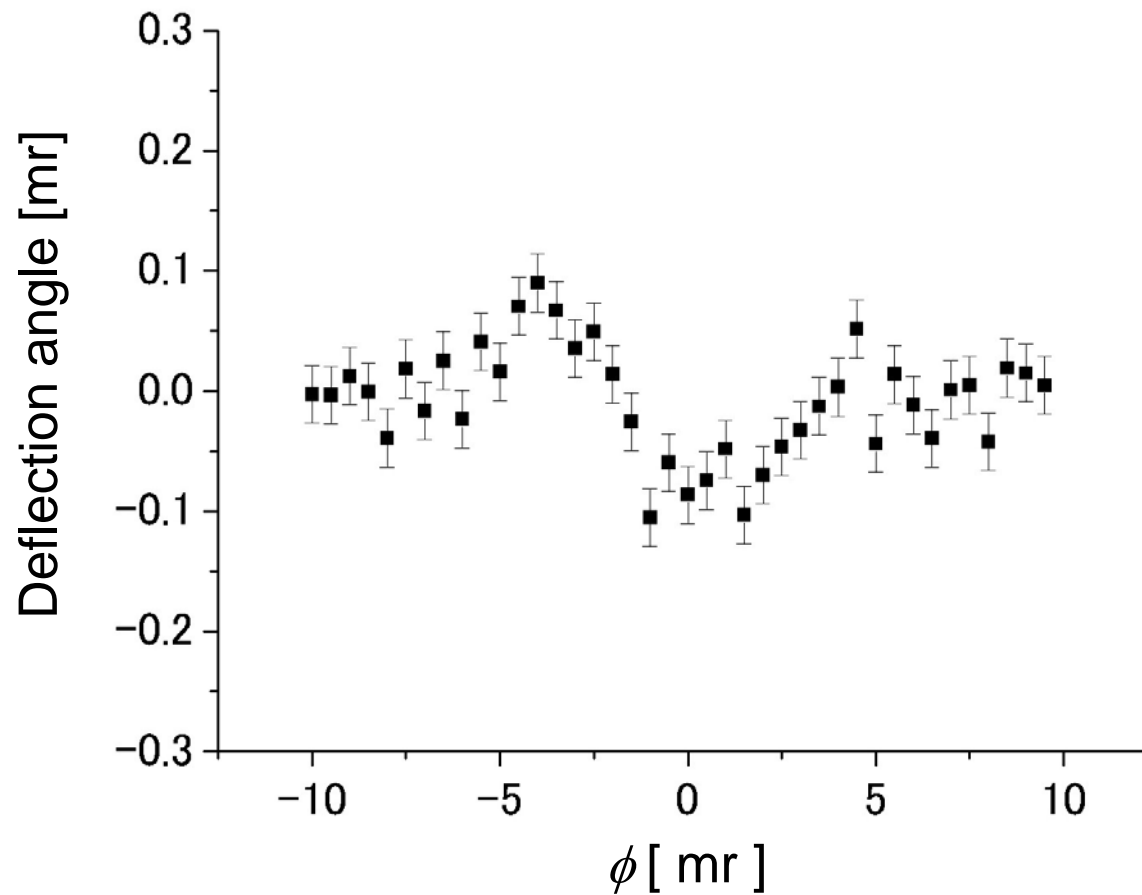
Deflection angle \leftarrow change of beam center + 2.34m



Results

(2)

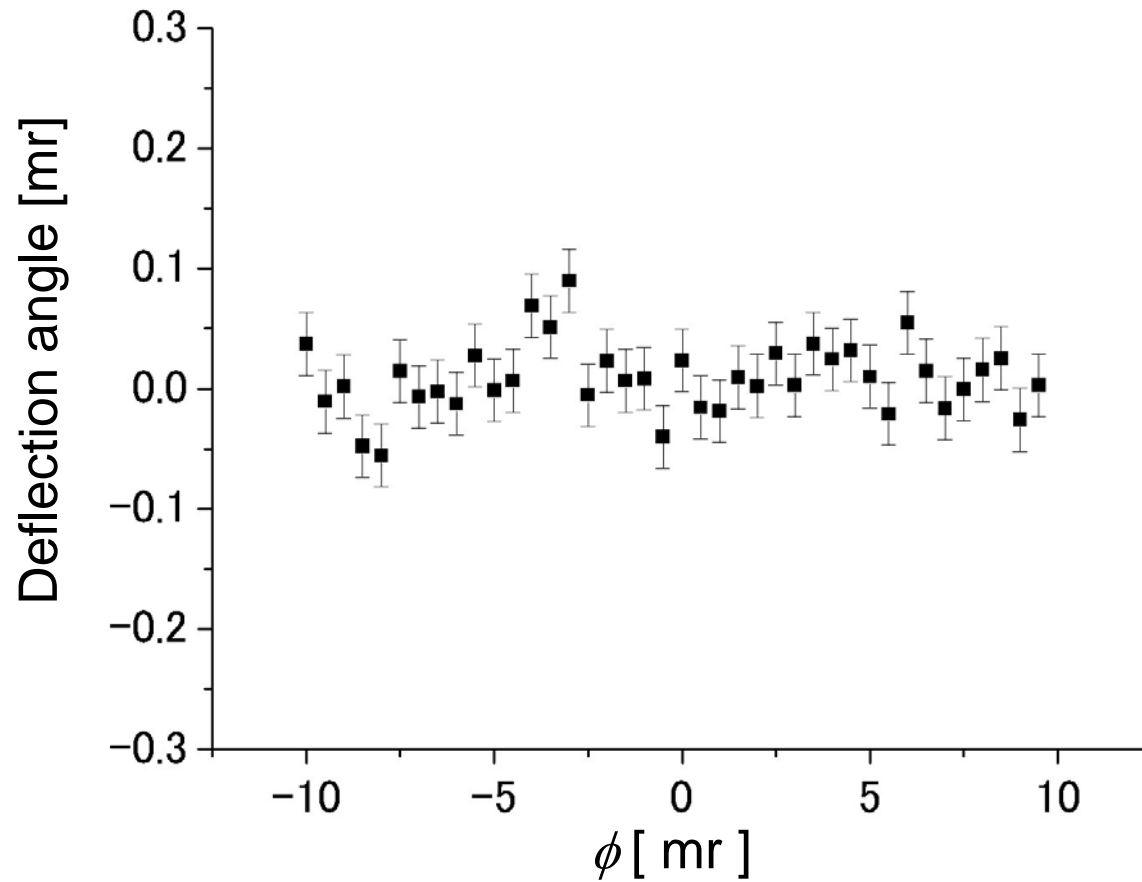
- Beam divergence = 3.8 mr $\theta = 0$ mr (QM3 : 2.2 A)



Results

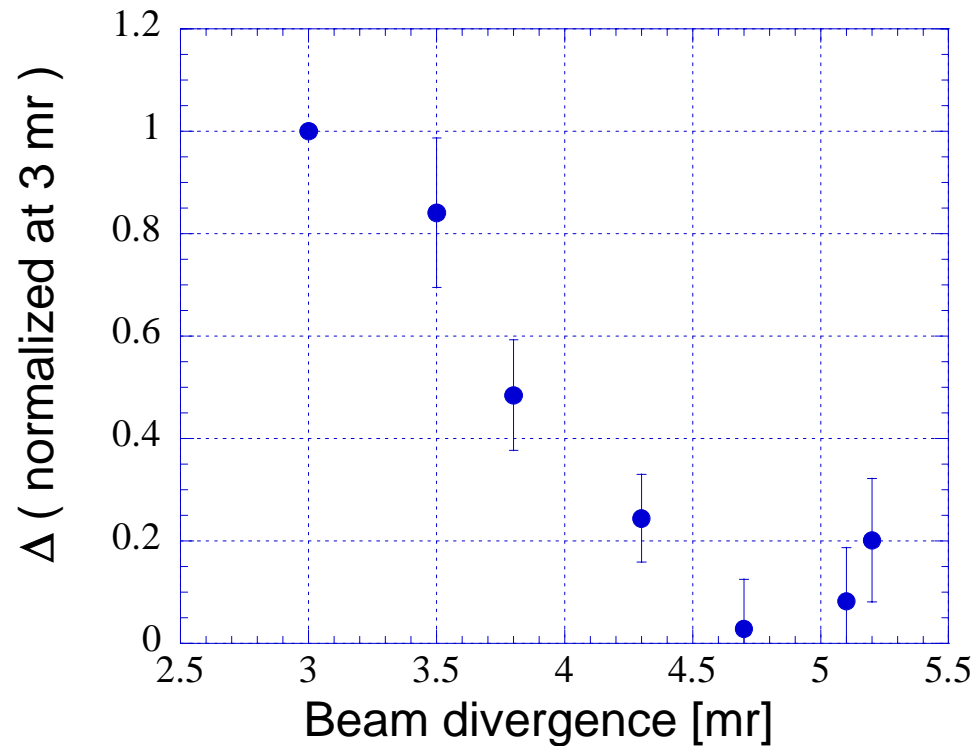
(3)

- Beam divergence : 5.2 mr $\theta = 0$ mr (QM3 : 2.6 A)

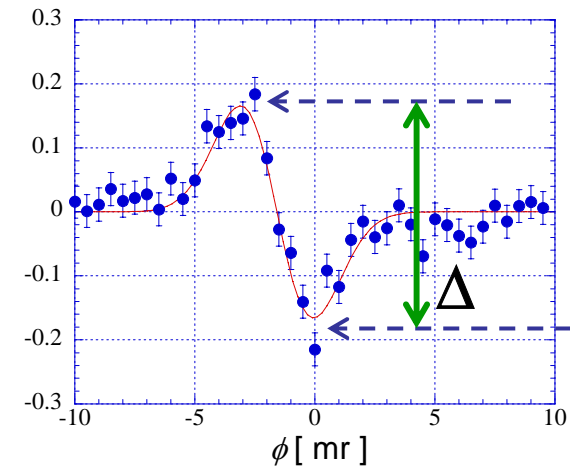


Results: deflection vs. beam divergence

- Deflection vs. beam divergence



The magnitude of the deflection, Δ , was determined by fitting the plot with 1st derivative of Gaussian function



Larger beam divergence \rightarrow Smaller deflection

Simulation

Lindhard string continuous potential

$$U = \frac{2Ze^2}{d} \ln \sqrt{1 + \frac{3R^2}{\rho^2}}$$

R : Thomas-Fermi radius

ρ : Distance from <100> axis

d : lattice constant in <100> axis
(5.43Å for Si)

Z : Atomic number (14 for Si)

Conditions for simulation

4th order of Runge-Kutta method

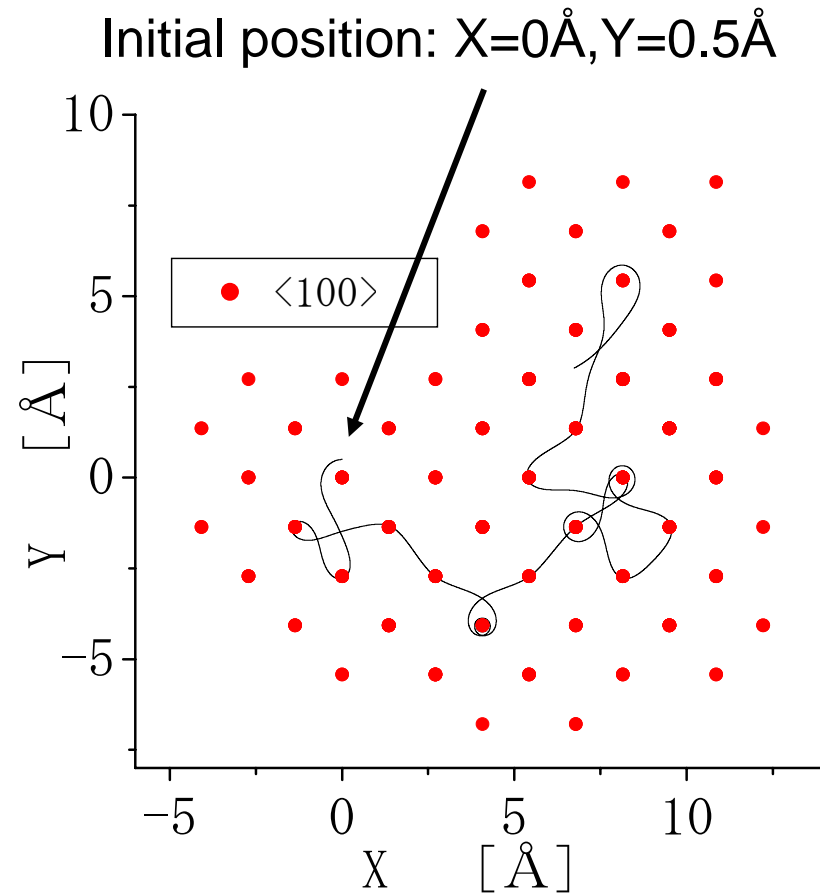
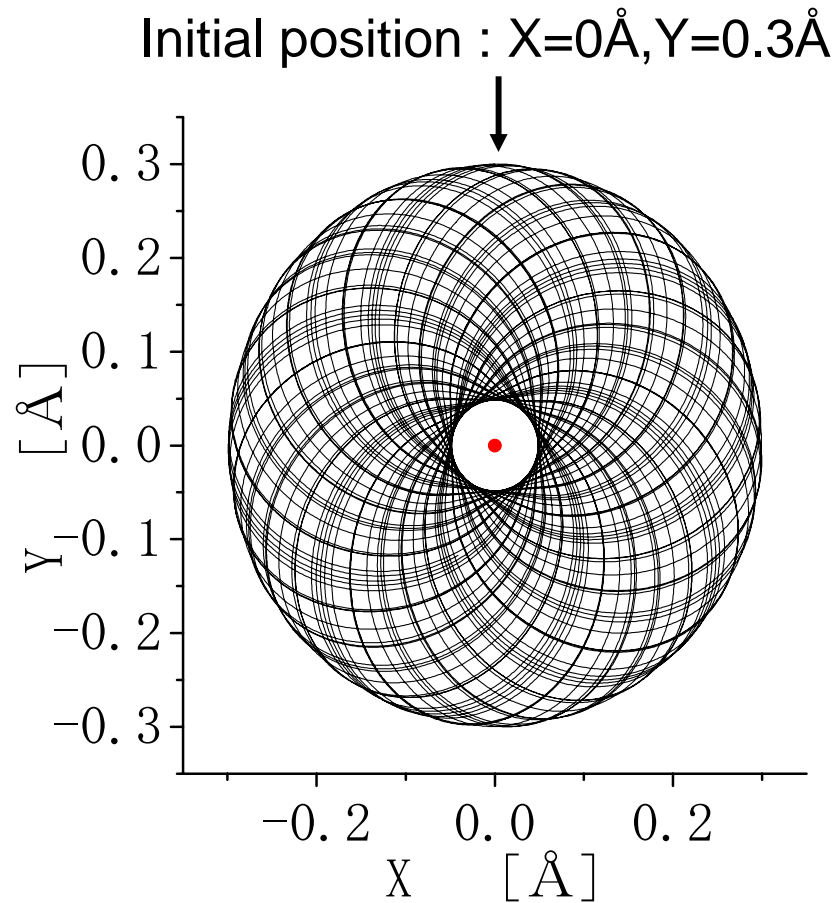
Without consideration of multiple scattering and channeling radiation

Energy of electrons : 150 MeV

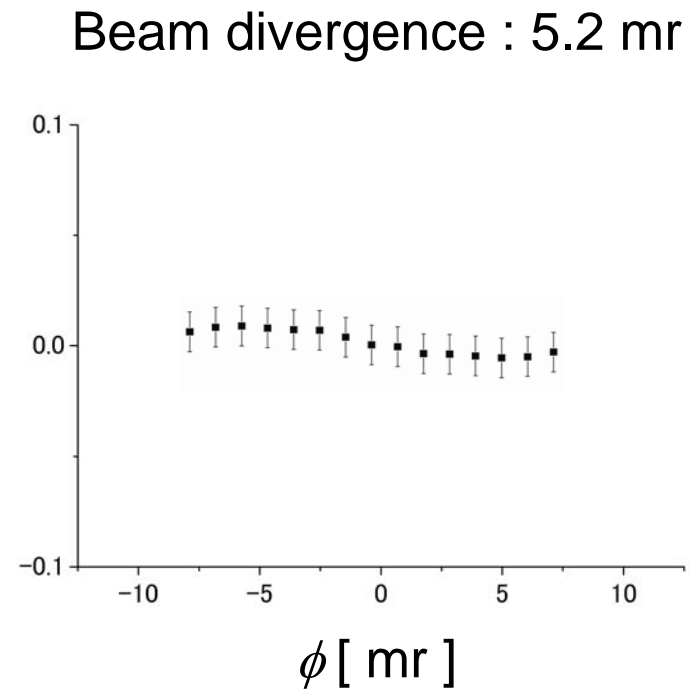
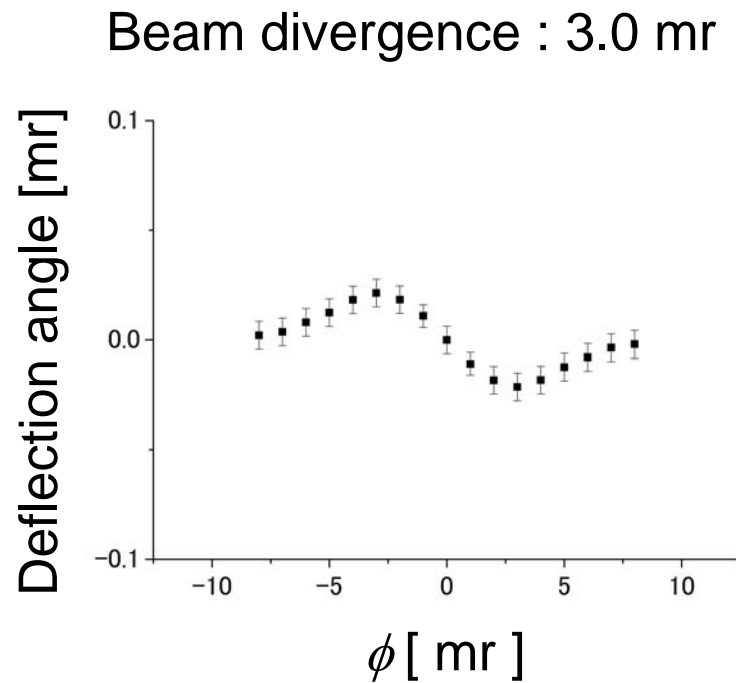
Thickness of the crystal : 16 μm

Simulation: trajectory

- Trajectory of an electron

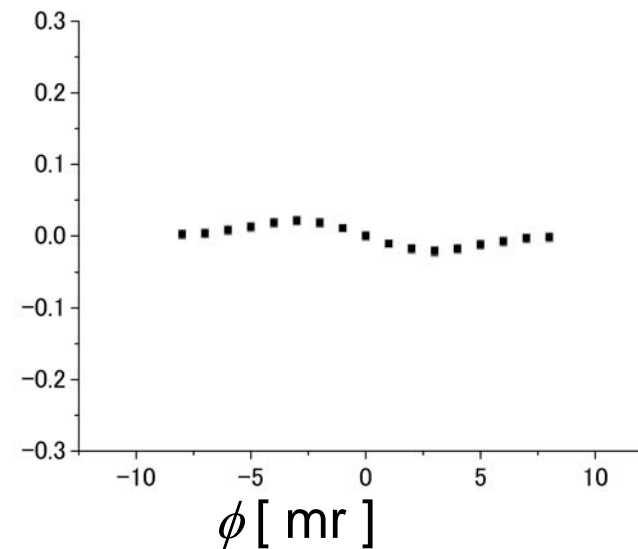
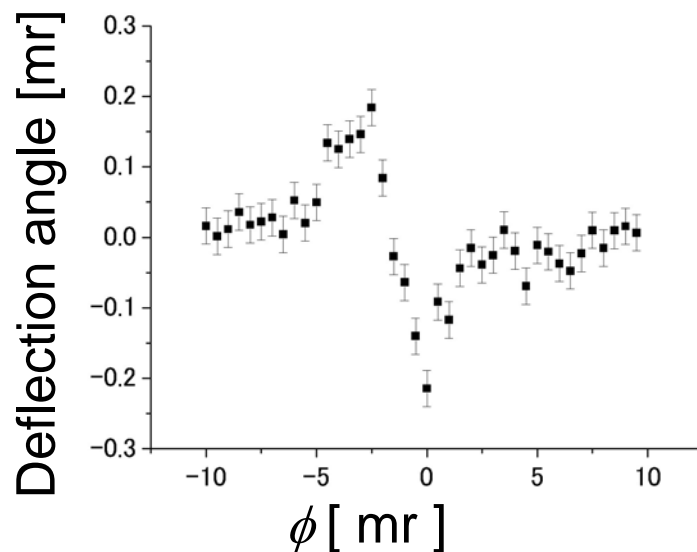


- Preliminary results



Larger beam divergence \rightarrow Smaller deflection

- Comparison with experimental data
 - Beam divergence : 3.0 mr (QM3 : 2.0 A)

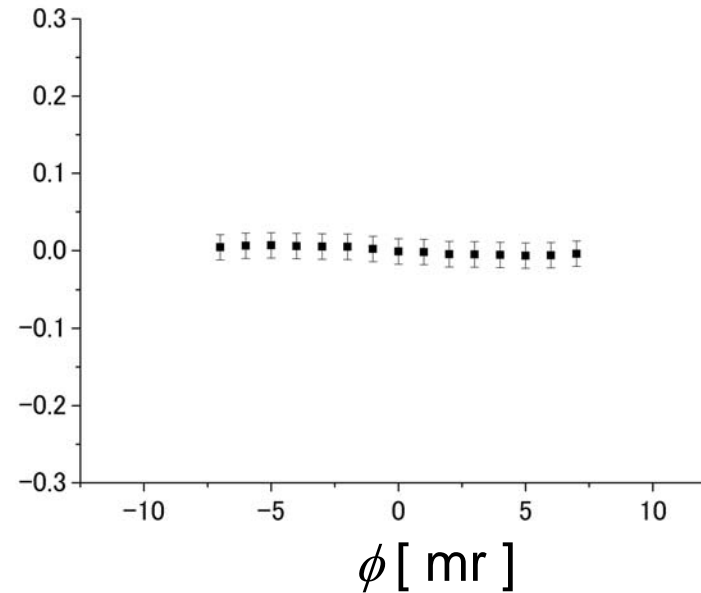
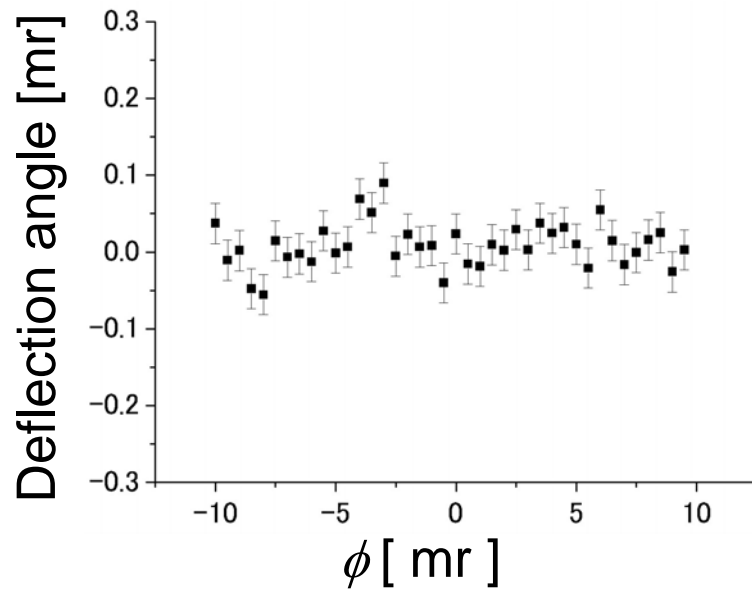


The tendency of the deflection as a function of the vertical direction of the crystal (ϕ) is same. But, in quantitative comparison, the peak-to-peak difference of the deflection angle of the measurement is about 0.4 mr, while it's around 0.04 mr for the simulation.

Simulation

(3)

- Comparison with experimental data
 - Beam divergence : 5.2 mr (QM3 : 2.6 A)



Experimental data agree with simulation qualitatively.
Study with more realistic beam profiles etc. is underway.

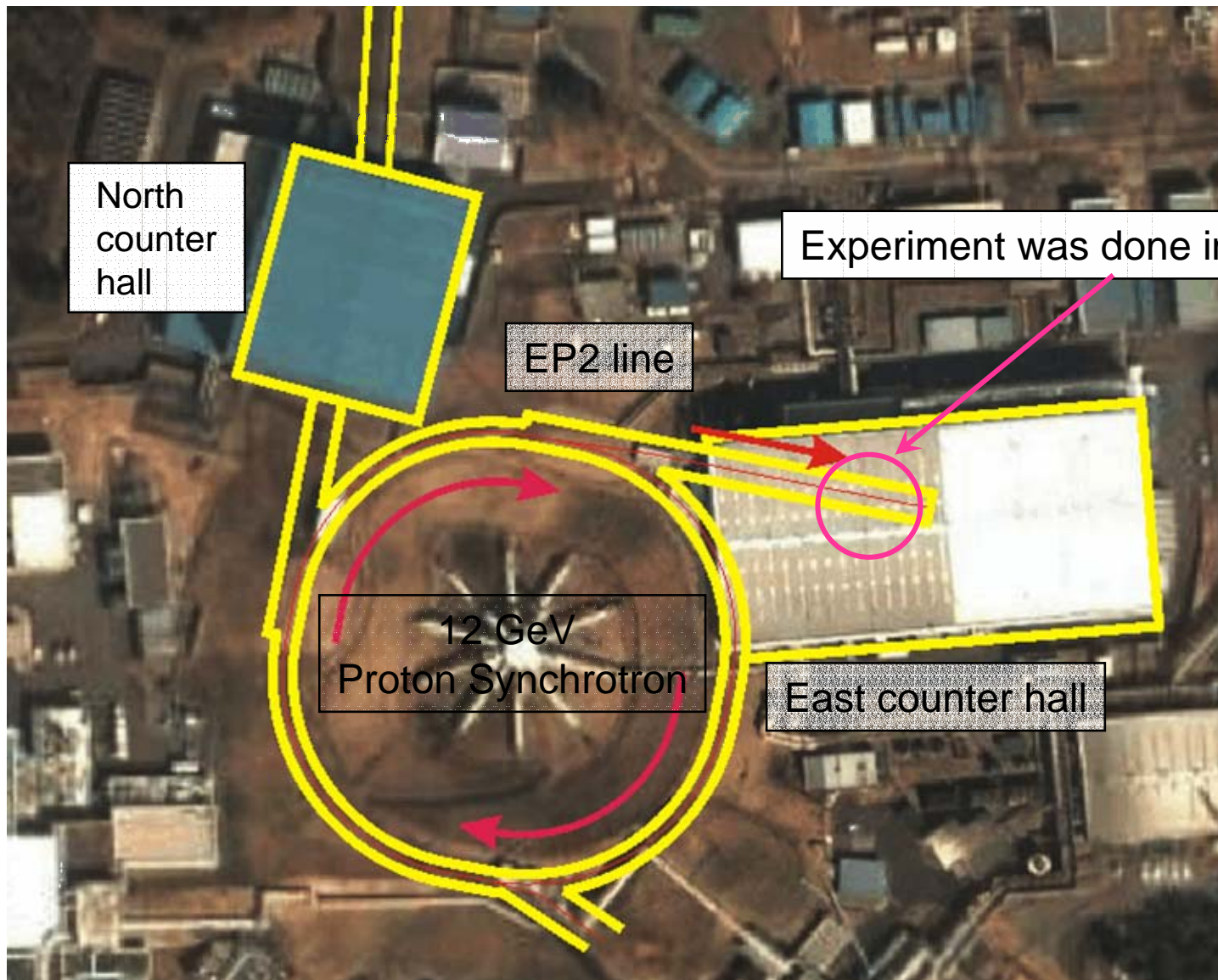
Summary

- Performed experiment on beam deflection at REFER with the 150-MeV electron beam.
- Systematic investigation of the beam deflection as a function of the beam divergence.
- Preliminary comparison with simulation:
 - Qualitative agreements
 - Quantitative comparison ... being studied

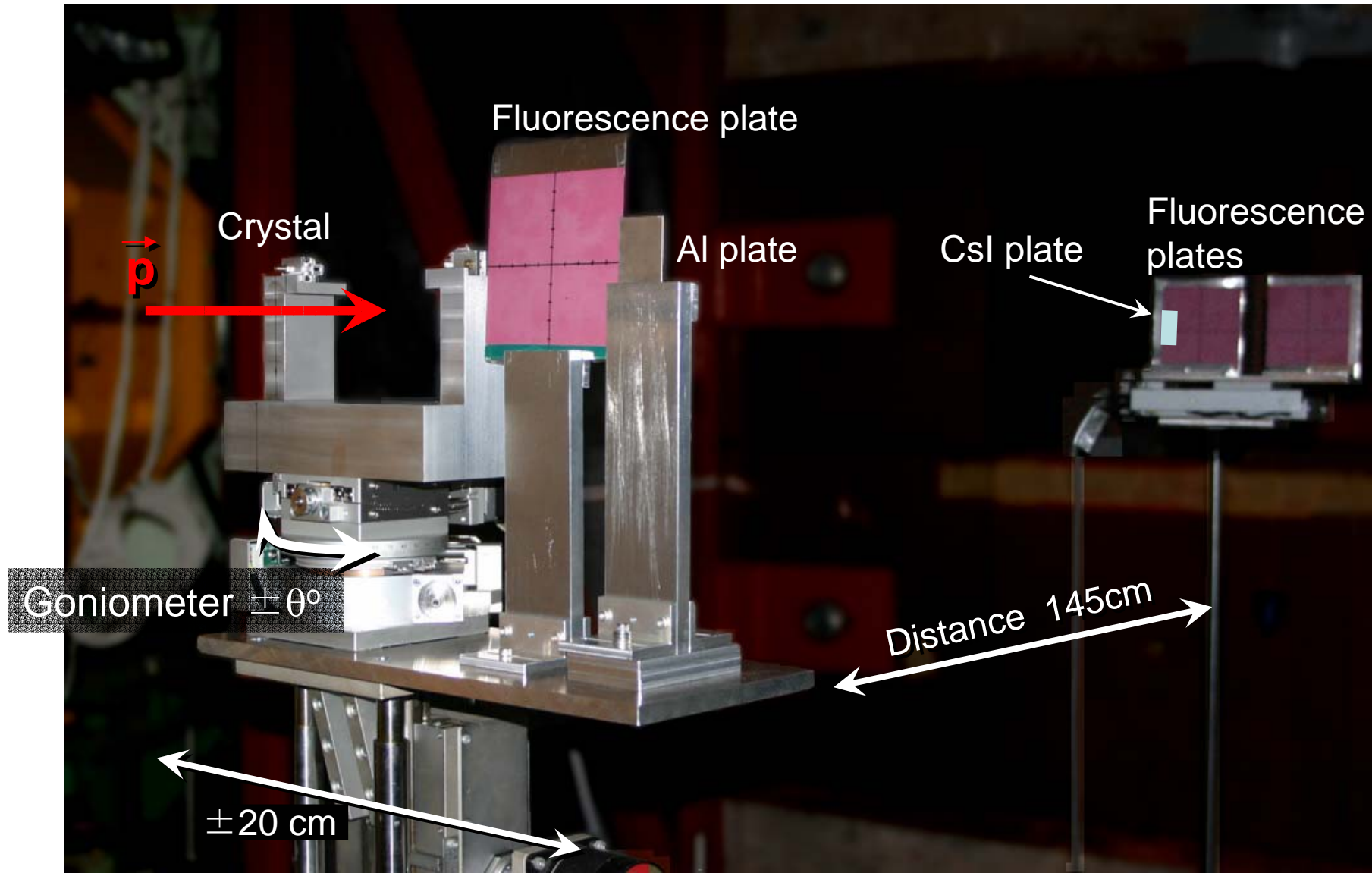
Prospect

- Experiment at KEK-ATF (Accelerator Test Facility)
 - $E = 1.28 \text{ GeV}$
 - Normalized emittance: $\varepsilon_x = 3.4 \times 10^{-6} \text{ m}$, $\varepsilon_y = 4.5 \times 10^{-8} \text{ m}$
 - Just a similar experiment at ATF as the REFER experiment
 - See channeling effects with the super-low emittance beam.

Experiment at KEK-PS



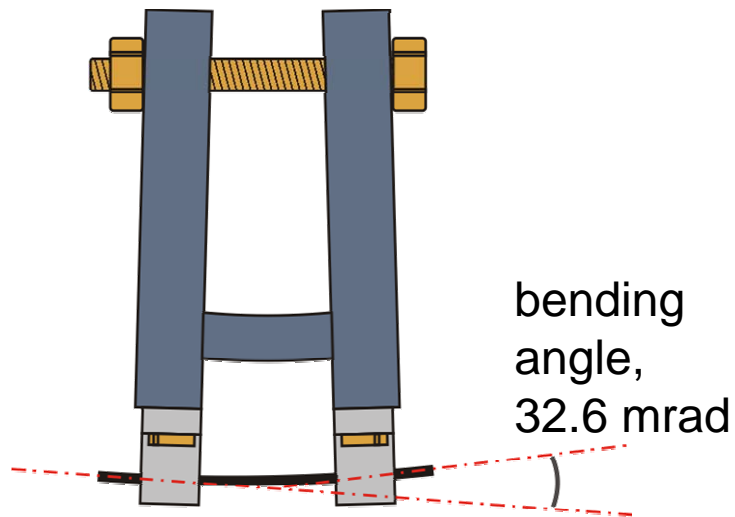
Experimental setup



Crystal, proton beam

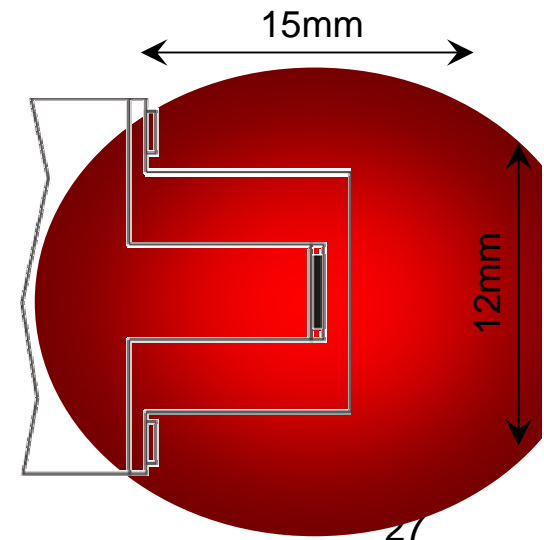
Parameters of crystal

Material: Silicon
Size: 3 x 0.3 x 10 mm
Bending angle: ~ 32.6 mrad
Plane: (111)
Lindhard angle: 0.066 mrad

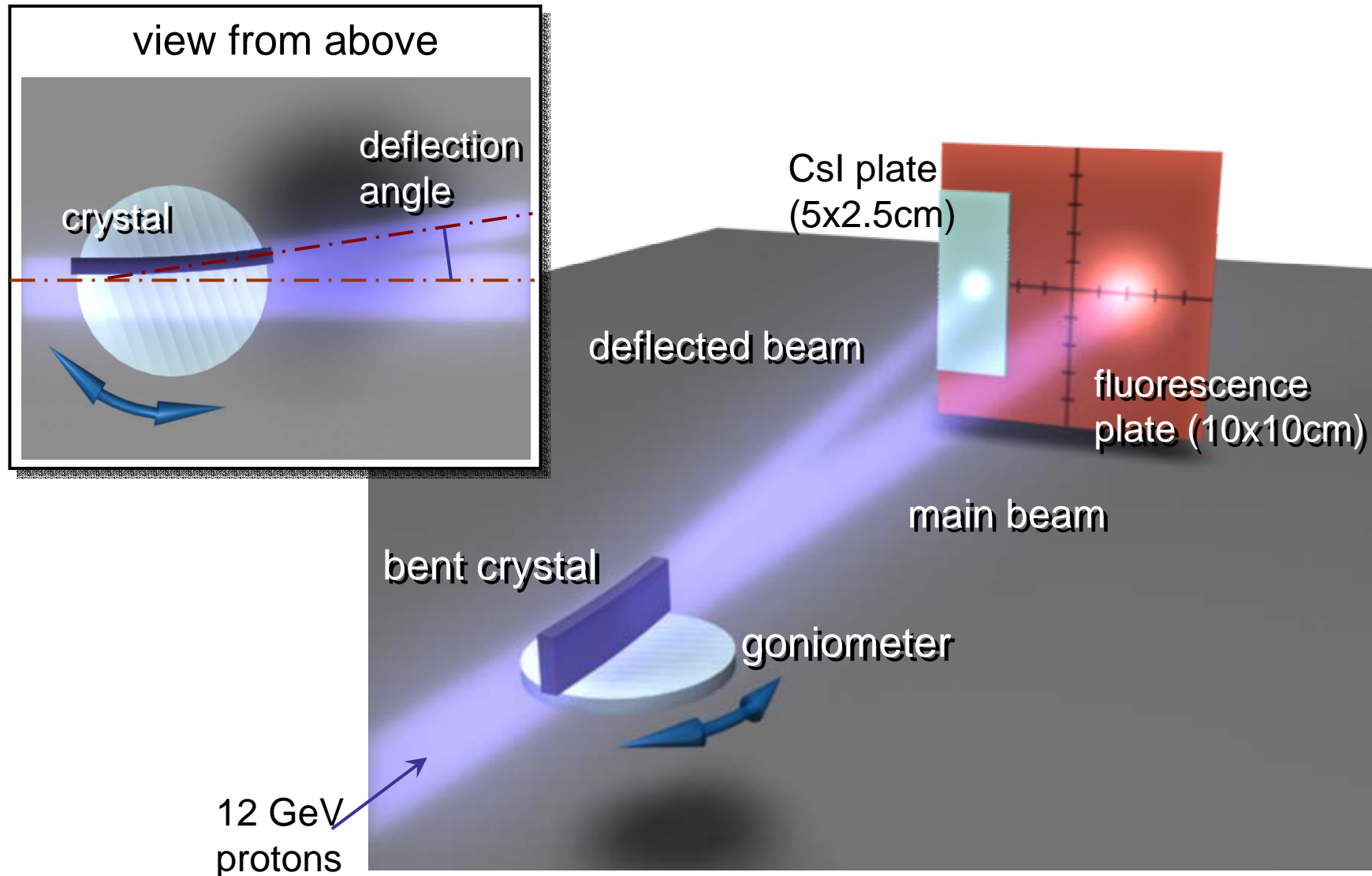


Parameters of the proton beam

Energy: 12 GeV
Intensity: 10^{12} protons/spill
Size: 15 x 12 mm
Divergence: < 5 mrad



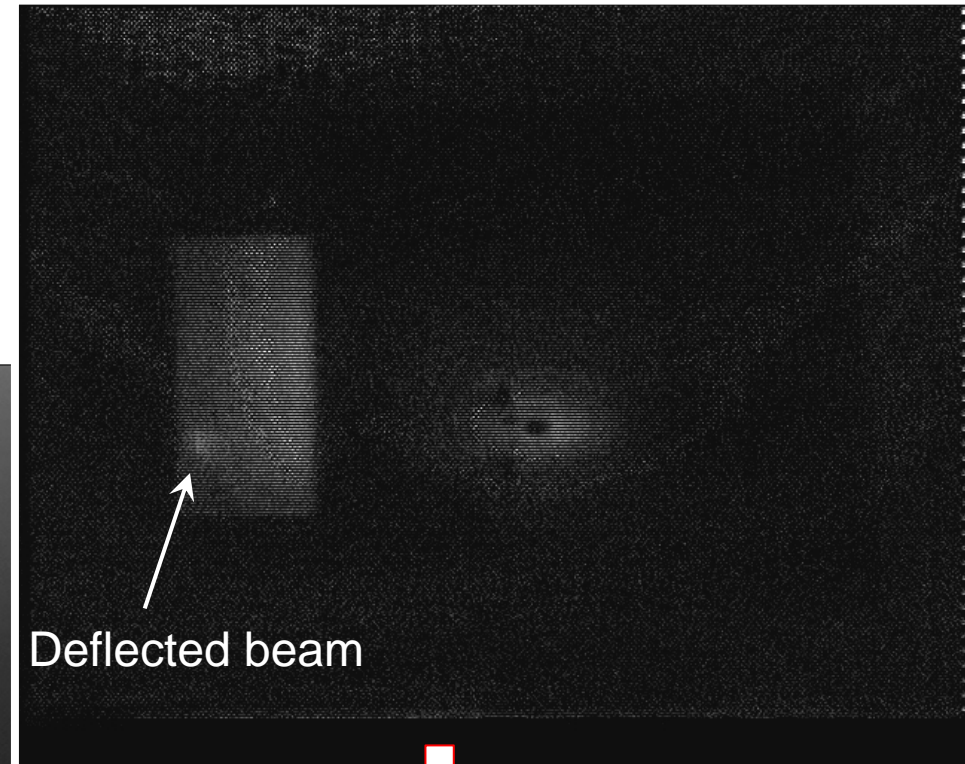
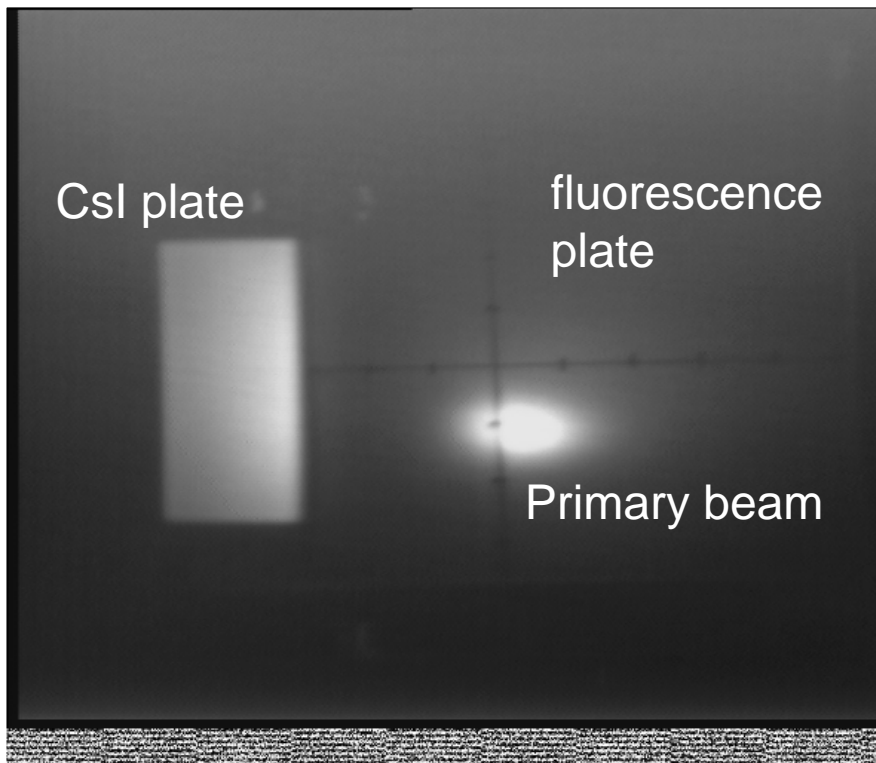
Schematic drawing of the experiment



Typical pictures

image after
background subtraction

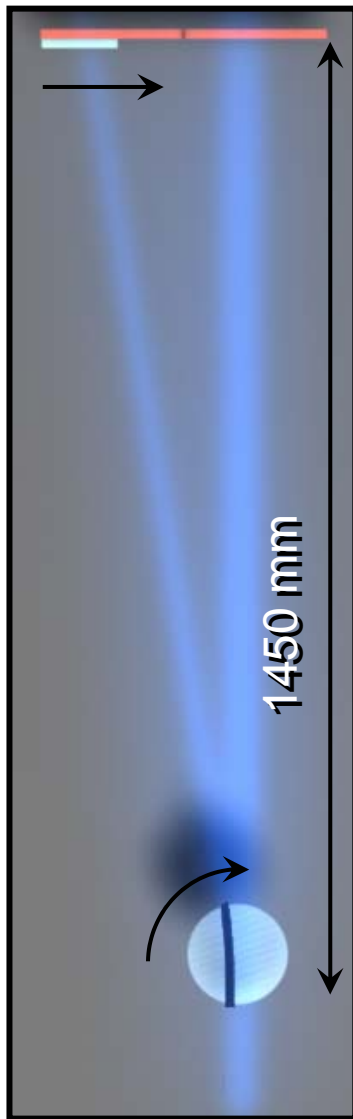
raw image



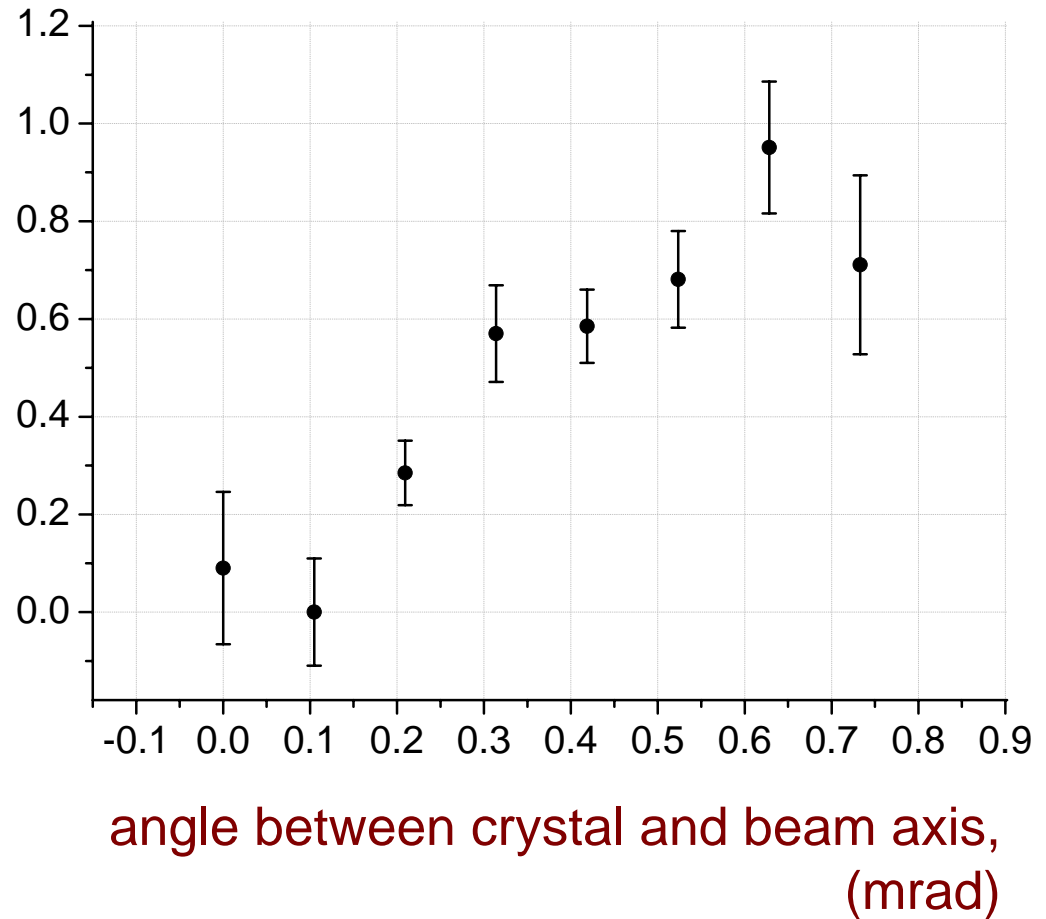
- intensity of deflected beam
- bending angle
- crystal efficiency

Results

(1)



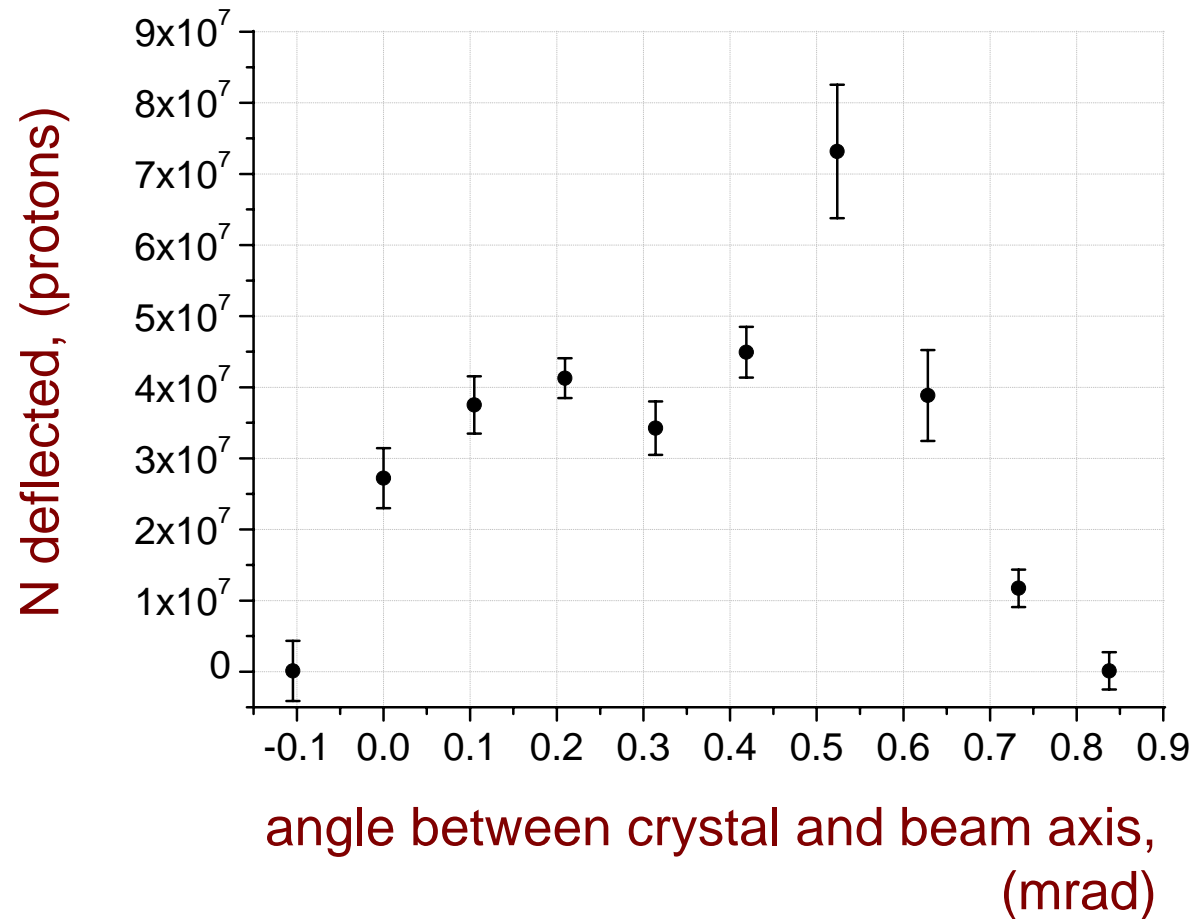
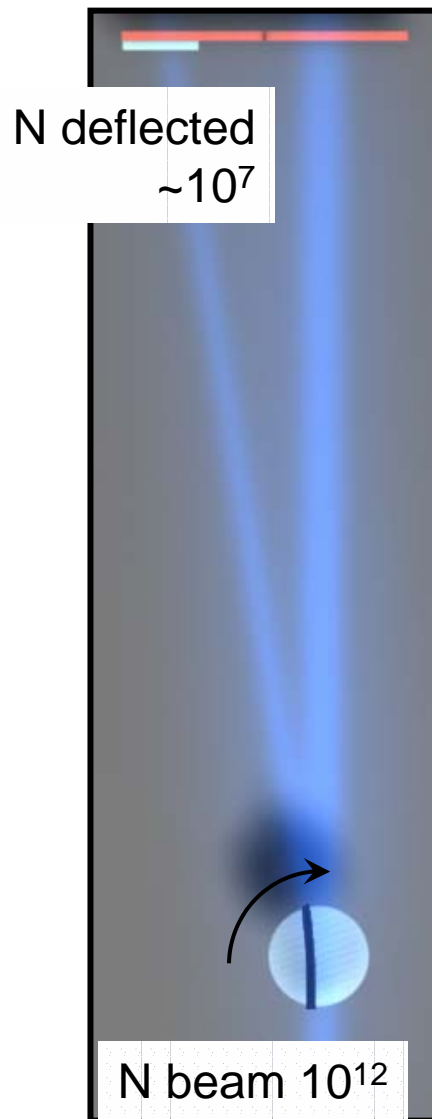
position of
deflected
beam on
CsI plate,
(mm)



Such dependence agrees with estimations

Results

(2)



10^{12} protons \rightarrow $\sim 10^7$ deflected protons

Crystal efficiency

$$N \text{ deflected} = \text{Crystal Efficiency} \times \text{Angle Efficiency} \times N \text{ incident upon the crystal.}$$



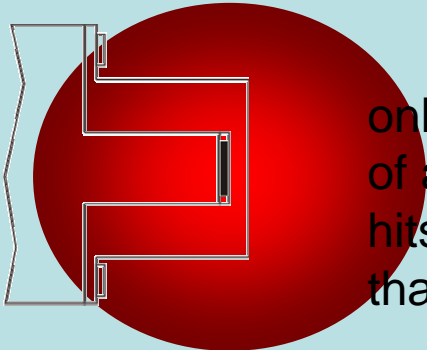
Crystal Efficiency could be:

100% → at 5 mrad

26% → at 1 mrad

13% → at 0.5 mrad

Incident particles within critical (Lindhard) angle to the crystallographic plane.
At the beam divergence <5 mrad and Lindhard angle 0.066 mrad, angle efficiency is > 1%



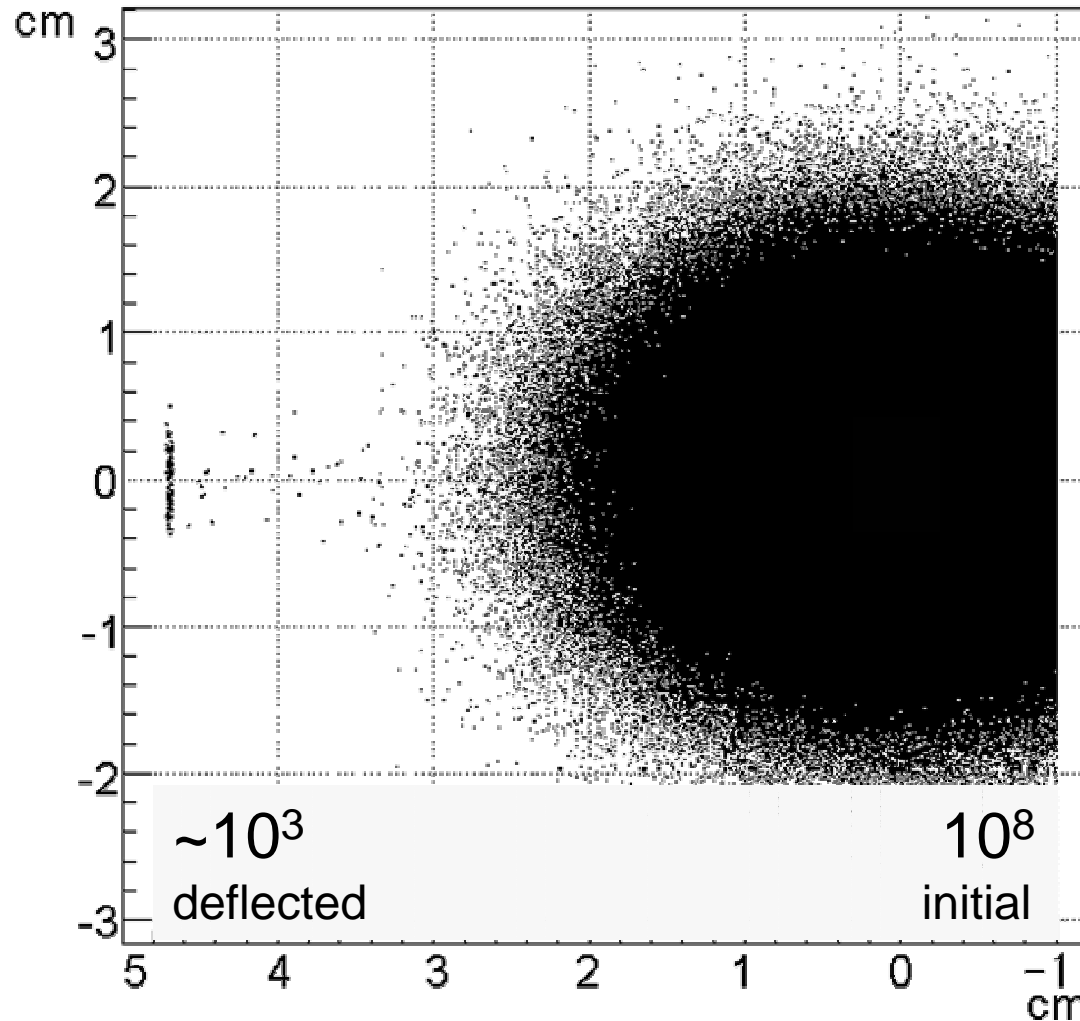
only small part of all protons hits crystal, that is 0.3%

$N \text{ incident upon the crystal} = 3 \times 10^9$

$N \text{ deflected} = 4 \times 10^7 \text{ protons}$

Simulation

picture at the distance 145 cm from the crystal



“Catch” code

Initial parameters

Beam

Energy: 12 GeV

Size: 15 x 12 mm

Divergence: 0.3, 0.5,
1, 5 mrad

Crystal

Size: 3 x 0.3 x 10 mm

Bending angle: ~ 32.6 mrad

Plane: (111)

10⁸ protons → ~ 10³ deflected protons

Simulation

$N \text{ deflected} = \text{Crystal Efficiency} \times$
 $\text{Angle Efficiency} \times$
 $N \text{ incident upon}$
 the crystal.

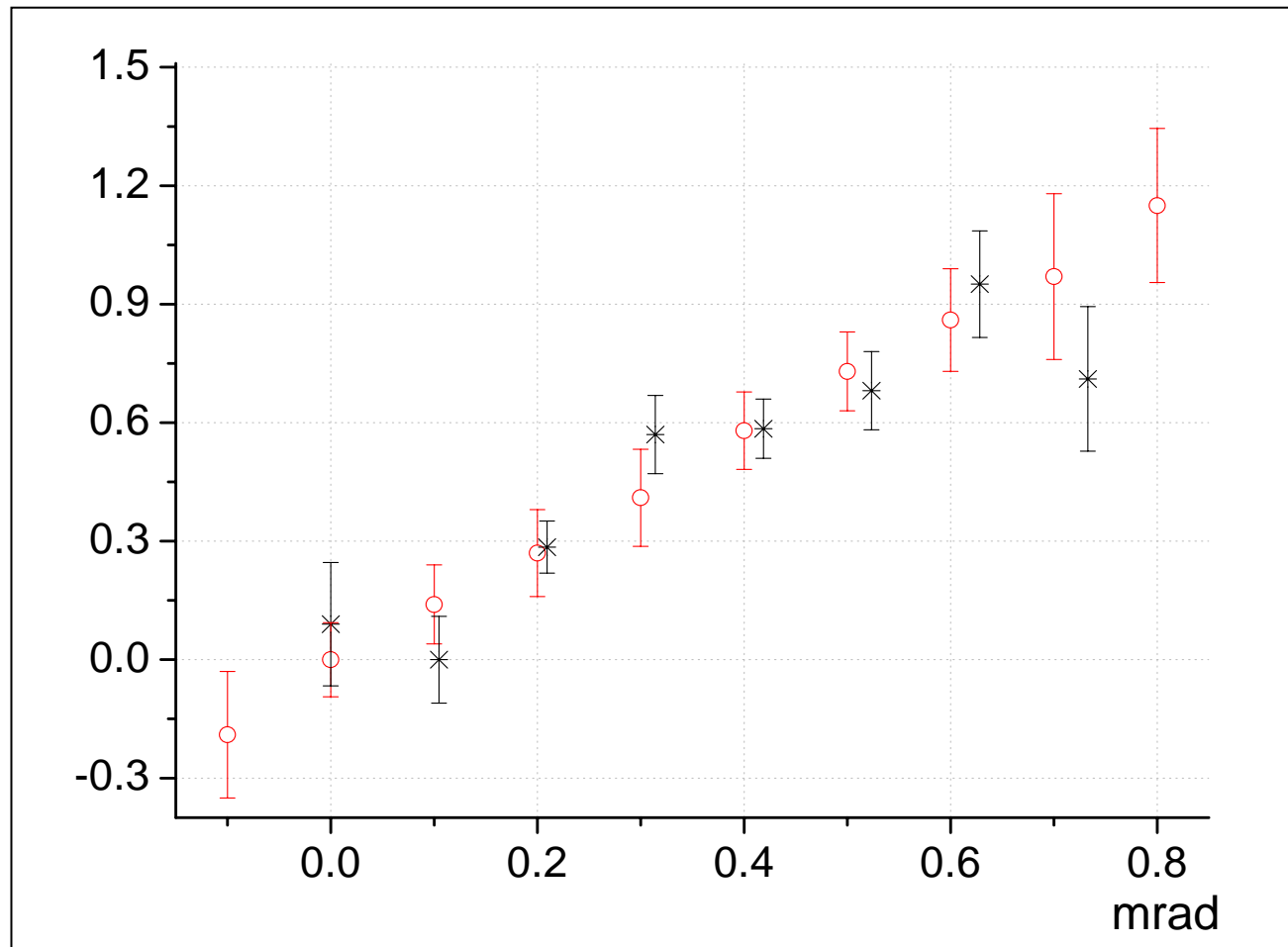


Crystal Efficiency is 15%

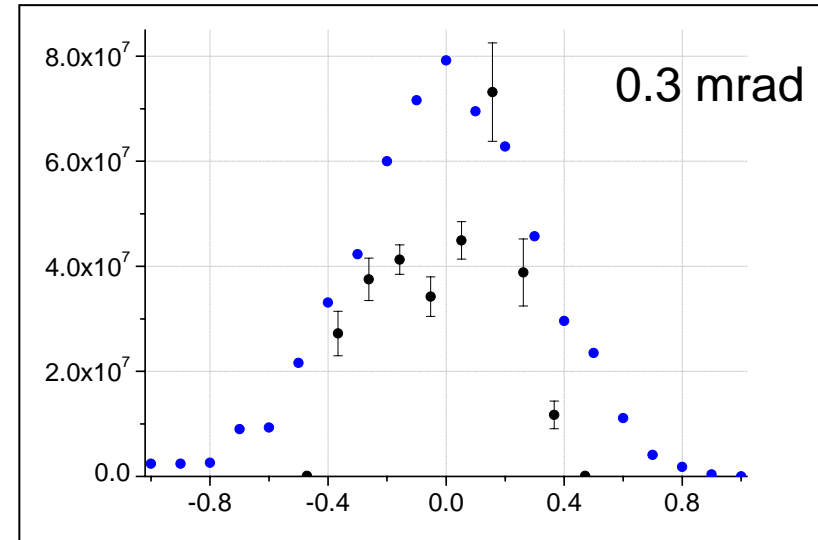
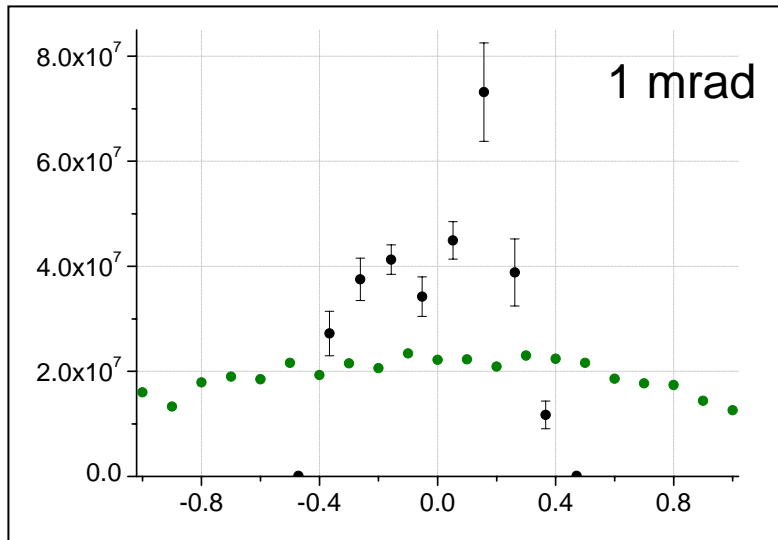
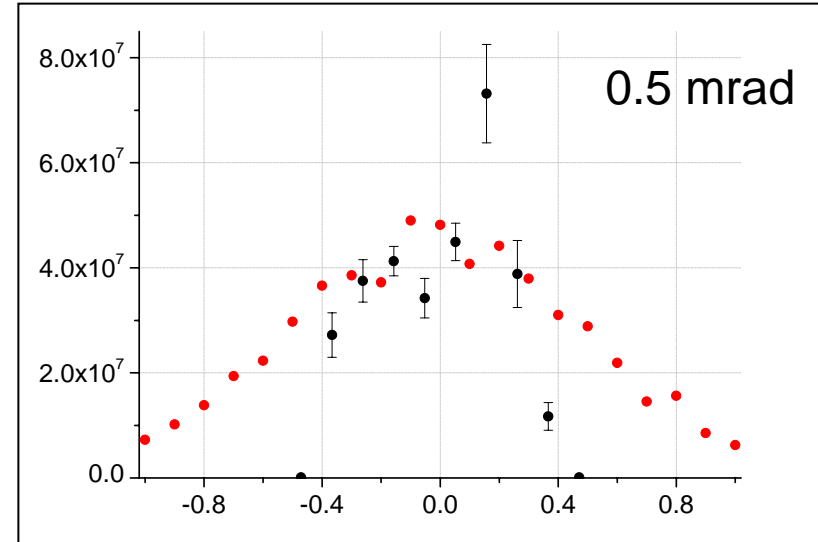
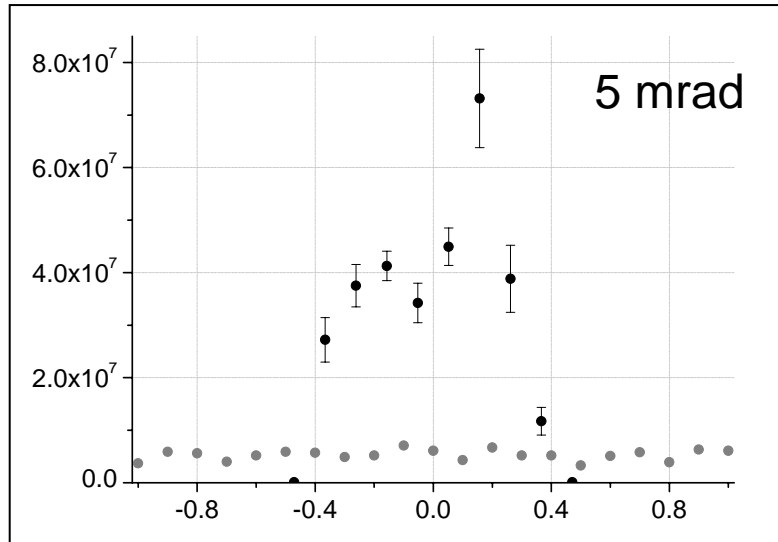
Simulation vs. Experimental data (1)

Position of the deflected beam
at the distance 145 cm from the crystal, (mm)

— experimental data
— simulation



Simulation vs. Experimental data (2)



Crystal efficiency

At the beam divergence 0.3 - 0.5 mrad
crystal efficiency in experiment was 8 - 13%

From the simulation it is 15%

Summary

- Experiment on the deflection of proton beam by the bent crystal was successfully done.
- The crystal shows good deflection efficiency which is 8 -13%.
- Performed Monte-Carlo simulation proves the experimental data

Future projects

Next experiment on the channeling of ultra-low emittance electron beam will be performed at KEK-ATF (Autumn, 2006).

Participation at the experiment on proton collimation at the Fermilab.

Experiment at the REFER ring, Hiroshima University with the 150 MeV electron beam (channeling radiation)

Application for the J-PARC